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Physical Properties and Applications of Photorefractive Materials

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Physical Properties and Applications of Photorefractive Materials

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OUTLINE

- Introduction to Nonlinear Optics
- The Photorefractive Effect
- Two- and Four-Wave Mixing
- Self- and Mutually-Pumped Phase Conjugators
- Photorefractive Materials
- Applications

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Introduction to Nonlinear Optics

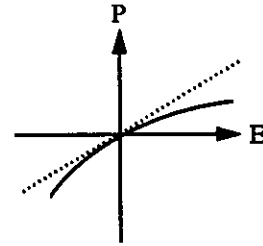
Induced polarization in a medium

$$\begin{aligned}
 \mathbf{P} &= \epsilon_0 \chi_{\text{linear}} \mathbf{E} + \epsilon_0 \chi^{(2)} \mathbf{E}\mathbf{E} + \epsilon_0 \chi^{(3)} \mathbf{E}\mathbf{E}\mathbf{E} + \dots \\
 &= \epsilon_0 \chi_{\text{linear}} \mathbf{E} + \epsilon_0 (\chi^{(2)} \mathbf{E} + \chi^{(3)} \mathbf{E}\mathbf{E} + \dots) \mathbf{E} \\
 &= \epsilon_0 \chi_{\text{linear}} \mathbf{E} + \epsilon_0 \chi_{\text{nonlinear}}(\mathbf{E}) \mathbf{E}
 \end{aligned}$$

where

$$\chi_{\text{linear}} = n_b^2 - 1$$

$$\chi_{\text{nonlinear}}(\mathbf{E}) = 2n_b \Delta n(\mathbf{E}) + (\Delta n(\mathbf{E}))^2 \approx 2n_b \Delta n(\mathbf{E})$$



Pockels (linear electrooptic) effect

$$n = n_b + \Delta n(\mathbf{E}) = n_b - \frac{1}{2} n_b^3 r E^{\Omega(\ll \omega)}$$

Optical Kerr effect

$$n = n_b + \Delta n(\mathbf{E}) = n_b + n_2 I$$

Photorefractive effect

$$n = n_b - \frac{1}{2} n_b^3 r E_{sc}$$

$$= n_b - \frac{1}{2} n_b^3 r E_{sc}^0 \left[\frac{2E_1^{\omega} (E_2^{\omega})^*}{I} \right]$$

Nonlinear Refraction: a comparison

Optical Kerr effect

i) nonresonant case

$$n_2 \approx 3 \times 10^{-16} \text{ cm}^2/\text{W} \text{ for glass (silica)}$$

ii) resonant case (exciton saturation)

$$n_2 \approx 2 \times 10^{-5} \text{ cm}^2/\text{W} \text{ for bulk GaAs at 300K}$$

$$4 \times 10^{-3} \text{ cm}^2/\text{W} \text{ for AlGaAs/GaAs MQWs}$$

Photorefractive effect

$$\Delta n/I \approx 1 \times 10^{-5} \sim 1 \times 10^{-4} \text{ cm}^2/\text{W} \text{ for typical bulk materials}$$

$$\sim 1 \times 10^{-3} \text{ cm}^2/\text{W} \text{ for some PR polymers}$$

The Photorefractive Effect

The Photorefractive Effect – charge-transport optical nonlinearity–

Discovered as “optical damage” in LiNbO_3 and LiTaO_3

[A.Ashkin *et al.*, Appl.Phys.Lett. 9, 72-74 (1966)]

Advantages

- large (nonlocal) nonlinearity with low-intensity cw light
- long interaction length possible due to low absorption
- broadband sensitivity

Disadvantages

- slow response speed (\propto intensity)
- bulky sample size

Requirements for being *photorefractive*

- electrooptic
- photoconductive
- low dark-conductive

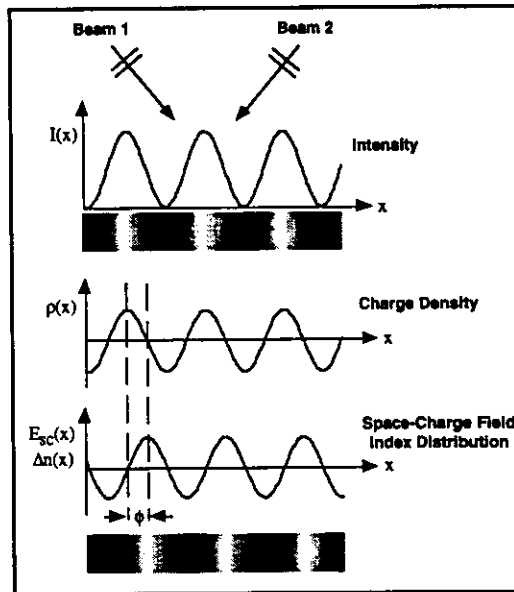
The Photorefractive Effect

- mechanism -

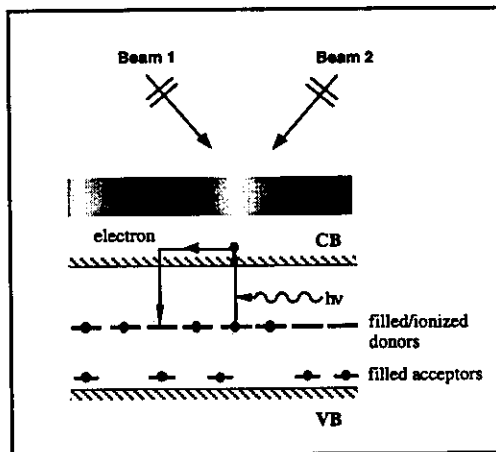
Fundamental processes for the photorefractive effect

- photoexcitation of carriers
- charge transport
- [- charge trapping]
- space-charge field formation
- refractive index changes via the electrooptic effect

This charge migration results in setting up high electric fields in a crystal on the order of kV/cm or even more !



Band-Transport Model



Mechanisms responsible for transporting carriers

i) diffusion

$$j_{diff} = De \nabla n$$

where

$$D = \mu k_B T / e$$

ii) drift

$$j_{drift} = \sigma E$$

where

$$\sigma = |e| \mu n$$

and

$$E = E_{sc} + E_0$$

iii) bulk photovoltaic effect

$$(j_{ph})_i = (\beta_{ijk} E_j E_k + c.c.) / 2$$

Band-Transport Equations

[N.V.Kukhtarev *et al.*, *Ferroelectrics* 22, 949-964 (1979)]

$$\frac{\partial N^+}{\partial t} = (\beta + sI)(N - N^+) - \gamma_R n N^+ \quad (\text{rate equation})$$

$$\frac{\partial N^+}{\partial t} = \frac{\partial n}{\partial t} - \frac{1}{e} \nabla \cdot \mathbf{j} \quad (\text{continuity equation})$$

$$\mathbf{j} = \mathbf{j}_{\text{diff}} + \mathbf{j}_{\text{drift}} + \mathbf{j}_{\text{ph}}$$

$$\nabla \cdot (\epsilon \mathbf{E}) = e(N^+ - N_A^- - n) \quad (\text{Poisson's equation})$$

$$\mathbf{E} = \mathbf{E}_{\text{sc}} + \mathbf{E}_0$$

where

N = total donor density

N^+ = ionized donor density

N_A^- = ionized acceptor density

n = electron density

β = dark (thermal) generation rate

s = photoionization cross section

γ_R = recombination coefficient

Linearization and Approximations

(Linearization)

Consider the solution in the following form:

$$\begin{aligned} F(z, t) &= F_0(t) + F_1(z, t) \\ &= F_0(t) + \frac{1}{2} F_1(t) \exp(-iKz) + \text{c.c.} \end{aligned}$$

Neglect the 2nd-order terms such as

$$\begin{aligned} n N^+ &= n_0 N_0^+ + n_0 N_1^+ + n_1 N_0^+ + n_1 N_1^+ \\ &\approx n_0 N_0^+ + n_0 N_1^+ + n_1 N_0^+ \end{aligned}$$

(Approximations)

$$n_0 \ll N_A^- \quad (\text{low - intensity excitation})$$

$$\frac{\partial n_0}{\partial t} = 0 \quad (\text{quasi - steady approximation})$$

Solution to Linearized Equations

For the intensity interference patterns

$$I(z) = I_0 + \frac{1}{2} I_1 \exp(-iKz) + \text{c.c.} = I_0 \left[1 + \frac{1}{2} m \exp(-iKz) + \text{c.c.} \right]$$

the transient solution of the space-charge field is given by

$$E_{sc}(z, t) = E_0 + \frac{1}{2} |E_{sc1}| e^{i\phi} \left(1 - e^{-t/\tau + i\omega_g t} \right) e^{-iKz} + \text{c.c.} \quad (m \ll 1)$$

where

$$|E_{sc1}| = \frac{m}{1 + \beta/sI_0} E_q \left[\frac{(E_0 - E_{ph})^2 + E_d^2}{E_0^2 + (E_d + E_q)^2} \right]^{1/2}$$

$$\phi = \tan^{-1} \left[\frac{(E_d + E_q)E_d + E_d(E_0 - E_{ph})}{E_q(E_0 - E_{ph}) - E_d E_{ph}} \right]$$

$$\tau = \tau_{di} \frac{(1 + E_d/E_\mu)^2 + (E_0/E_\mu)^2}{(1 + E_d/E_q)(1 + E_d/E_\mu) + E_0^2/E_q E_\mu}$$

$$\omega_g = \frac{1}{\tau_{di}} \frac{E_0/E_q - E_0/E_\mu}{(1 + E_d/E_\mu)^2 + (E_0/E_\mu)^2}$$

(diffusion field)

(saturation field)

$$E_d = k_B T K / e, \quad E_q = e N_{eff} / \epsilon K$$

(mobility field)

$$E_\mu = \gamma_R N_A^- / \mu K$$

(photovoltaic field)

$$E_{ph} = p \gamma_R N_A^- / e \mu s$$

(dielectric relaxation time)

$$\tau_{di} = \epsilon / e \mu n_0$$

(effective trap density)

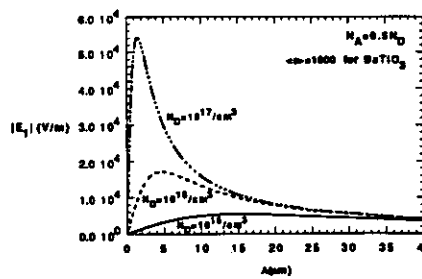
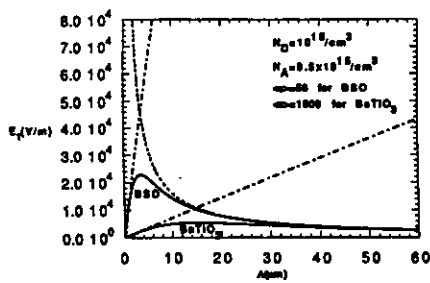
$$N_{eff} = N_A^- (N - N_A^-) / N$$

Steady-State Space-Charge Field – diffusion operation ($E_0 = 0$) –

$$|E_{sc1}| = \frac{m}{1 + \beta/sI_0} \frac{E_q E_d}{E_d + E_q}$$

$$\rightarrow |E_{sc1}|_{\max} = \frac{m}{1 + \beta/sI_0} \frac{1}{2} \left(\frac{k_B T N_{eff}}{\epsilon} \right)^{1/2} \text{ when } E_d = E_q \left[\text{i.e., } \Lambda = \Lambda_{\text{Debye}} = \frac{2\pi}{e} \left(\frac{k_B T \epsilon}{N_{eff}} \right)^{1/2} \right]$$

$$\phi = \frac{\pi}{2}$$

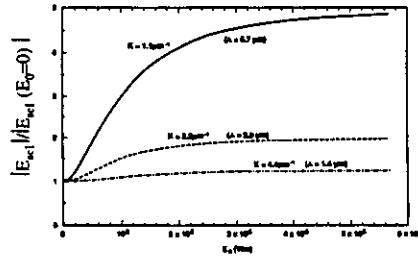


P. Yeh, Introduction to PR NLO(1993)

Steady-State Space-Charge Field – drift operation ($E_0 \neq 0$) –

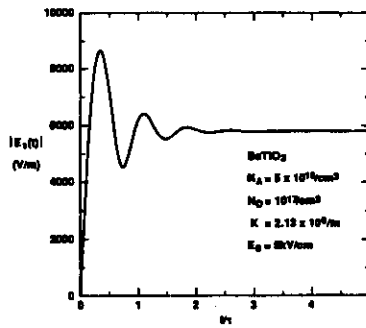
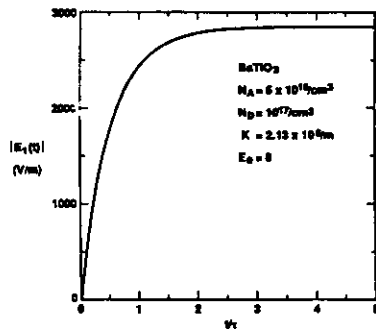
$$|E_{sc}| = \frac{m}{1 + \beta/sl_0} \left(\frac{E_q E_d}{E_d + E_q} \right) \left[\frac{1 + (E_0/E_d)^2}{1 + (E_0/(E_d + E_q))^2} \right]^{1/2}$$

$$\phi \neq \frac{\pi}{2} \quad \text{but } \phi \rightarrow \frac{\pi}{2} \quad \text{when } E_0 \gg E_d, E_q$$



P.Yeh, Introduction to PR NLO(1993)

Space-Charge Field – transient behavior –



P.Yeh, Introduction to PR NLO(1993)

Effective Electrooptic Coefficient

The electrooptic effect is formally defined as a change in the optical impermeability tensor $\tilde{\eta}$ ($\equiv \epsilon_0 \tilde{\epsilon}^{-1}$)

$$\begin{aligned} \Delta \tilde{\eta}_{ij} &\equiv \tilde{\eta}_{ij}(E^\Omega) - \tilde{\eta}_{ij}(0) \\ &= \epsilon_0 [\tilde{\epsilon}(E^\Omega)^{-1}]_{ij} - \epsilon_0 [\tilde{\epsilon}(0)^{-1}]_{ij} \\ &= -\epsilon_0 [\tilde{\epsilon}^{-1} : \Delta \tilde{\epsilon} : \tilde{\epsilon}^{-1}]_{ij} \\ &= \tilde{r}_{ijk} E_k^\Omega + \tilde{s}_{ijkl} E_k^\Omega E_l^\Omega \end{aligned}$$

For the first-order electrooptic (Pockels) effect

$$\Delta \tilde{\epsilon} = -\epsilon_0^{-1} E^\Omega [\tilde{\epsilon} : (\tilde{r} : \mathbf{e}_E) : \tilde{\epsilon}]$$

Photorefractive refractive index grating formed by two-beam interference

$$\Delta \tilde{n} \approx \frac{1}{2\epsilon_0 n} (\mathbf{e}_1^* : \Delta \tilde{\epsilon} : \mathbf{e}_2)$$

$$\equiv -\frac{1}{2} n^3 \tilde{r}_{\text{eff}} E_{sc}$$

where

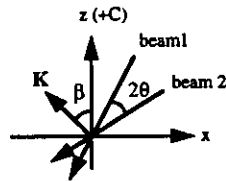
$$n = n_e n_o [n_e^2 \sin^2 \theta + n_o^2 \cos^2 \theta]^{1/2}$$

For 4mm symmetry crystals (e.g., BaTiO₃ and SBN)

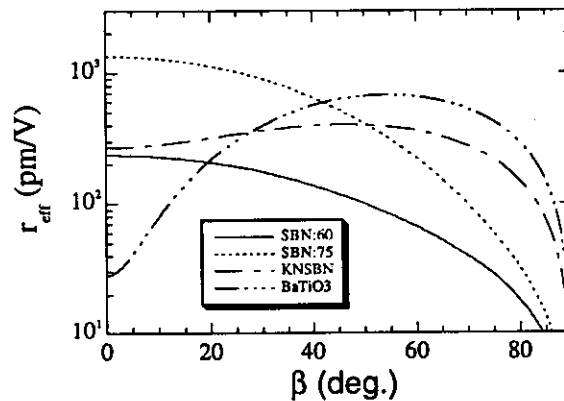
$$r_{\text{eff}} = r_{13} \cos \beta \quad \text{for s-polarized beams}$$

$$r_{\text{eff}} = \{n_e^4 r_{33} \cos(\beta - \theta) \cos(\beta + \theta) + 2n_e^2 n_o^2 r_{42} \sin^2 \beta + n_o^4 r_{13} \sin(\beta - \theta) \sin(\beta + \theta)\} (\cos \beta / n^4)$$

for p-polarized beams

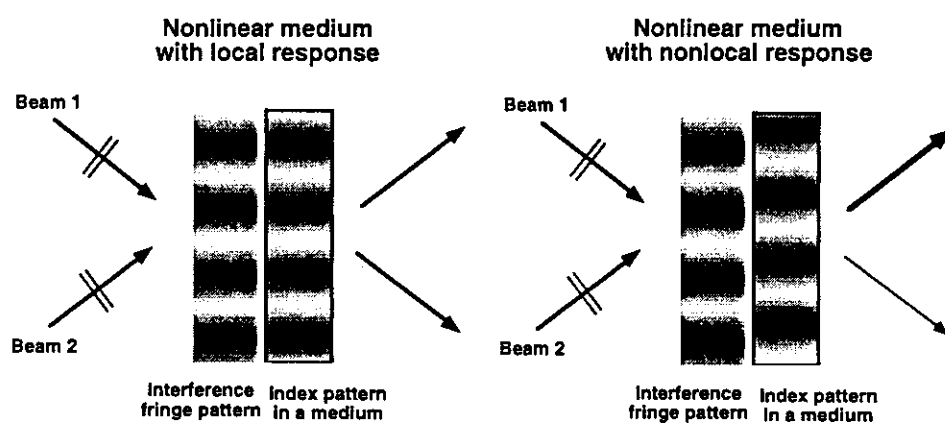


Effective Electrooptic Coefficient

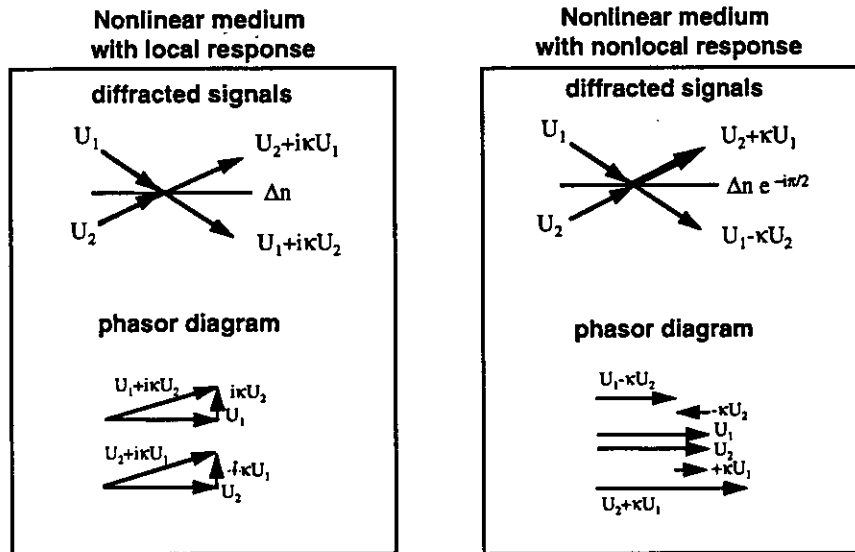


Photorefractive Two-Wave Mixing

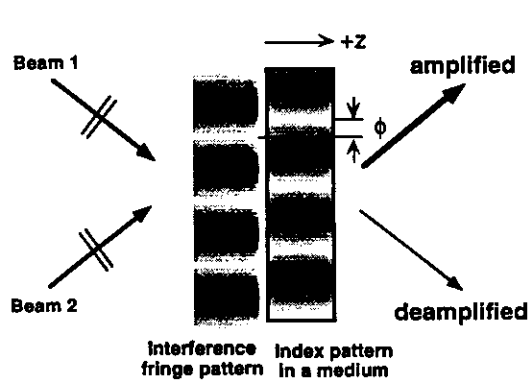
Two-Wave Mixing



Diffraction Properties in Two-Wave Mixing



Two-Beam Coupling in a Photorefractive Medium



$$\frac{dI_1}{dz} = -\alpha I_1 - 2\gamma' \frac{I_1 I_2}{I_1 + I_2}$$

$$\frac{dI_2}{dz} = -\alpha I_2 + 2\gamma' \frac{I_1 I_2}{I_1 + I_2}$$

$$\frac{d(\phi_1 - \phi_2)}{dz} = \gamma'' \frac{I_1 - I_2}{I_1 + I_2}$$

where

$$\gamma' = \frac{2\pi n_1}{\lambda \cos \theta} \sin \phi$$

$$\gamma'' = \frac{\pi n_1}{\lambda \cos \theta} \cos \phi$$

$$n_1 = -\frac{1}{2m} n^3 r_{\text{eff}} |E_{\text{sc1}}|$$

Note that ϕ is determined by the crystal's orientation and the sign of carriers.

Two-Beam Coupling in a Photorefractive Medium

General solutions

$$I_1(z) = \frac{\beta I_0}{\beta + \exp(\Gamma z)} \exp(-\alpha z)$$

$$I_2(z) = \frac{I_0}{1 + \beta \exp(-\Gamma z)} \exp(-\alpha z)$$

$$\Delta\varphi(z) = \Delta\varphi(0) + \frac{1}{2} \cot \phi \ln \left\{ \frac{(1 + \beta)^2 \exp(-\Gamma z)}{[\beta + \exp(-\Gamma z)]^2} \right\}$$

where

$$I_0 = I_1(0) + I_2(0)$$

$$\beta = \frac{I_1(0)}{I_2(0)}$$

$$\Gamma = 2\gamma' = \text{exponential coupling gain coefficient}$$

Important properties

- i) $|\phi| = \pi/2$ (diffusion operation)
- *maximum* nonreciprocal energy transfer
 - *no* phase crosstalk

- ii) $0 \leq |\phi| < \pi/2$ (drift operation)
- nonreciprocal energy transfer for $\phi \neq 0$
 - phase crosstalk

Limiting cases

- i) $\phi \neq 0$ and $\beta \exp(-\Gamma z) \gg 1$

$$I_2(z) \approx I_2(0) \exp[(\Gamma - \alpha)z]$$

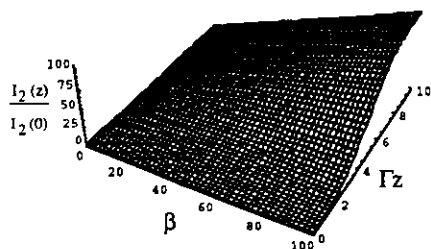
- ii) $\phi = 0$

$$\Delta\varphi(z) = \Delta\varphi(0) + \frac{1 - \beta}{1 + \beta} \frac{\Gamma z}{2}$$

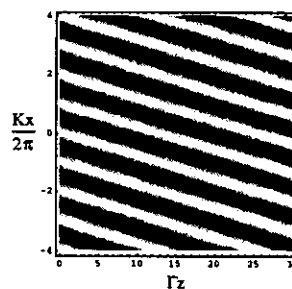
- iii) $\beta \gg 1$

$$\Delta\varphi(z) = \Delta\varphi(0) - \frac{1}{2} \Gamma z \cot \phi$$

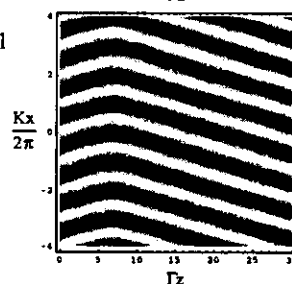
Numerical Examples



$\beta = 1000$
 $\phi = \pi/4$



$\beta = 0.001$
 $\phi = \pi/4$



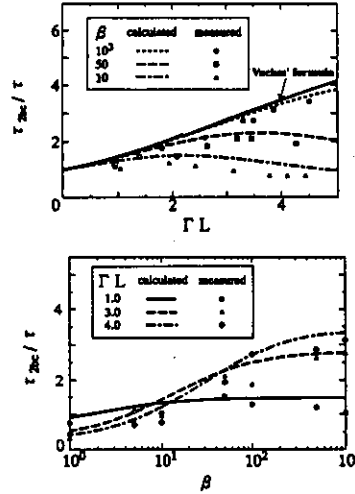
Photorefractive Response Time (τ) vs. Two-Beam Coupling Buildup Time (τ_{2bc})

Determination of τ is important for estimating photorefractive parameters such as $\mu\tau_R$. But the 2WM buildup time τ_{2bc} is usually different from τ .

Relationship between τ and τ_{2bc} for $\beta \gg 1$

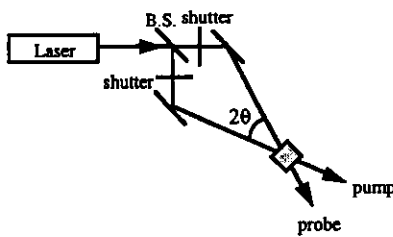
$$\tau_{2bc} \approx \begin{cases} \tau \{ 1 + 0.41\Gamma L + 0.074(\Gamma L)^2 + O[(\Gamma L)^3] \}, & \text{for } \Gamma L < 2.2 \\ \tau \frac{\Gamma L}{2} \{ 1 + [(1 - 1/e)^{1/2} - 1/2] (8\pi / \Gamma L)^{1/2} + O[(1/\Gamma L)] \}, & \text{for } \Gamma L > 2.2 \end{cases}$$

(Vachss, 1990)



Matsushima and Tomita, Opt. Commun. 128, 287 (1996)

Experimental Setup



Theoretical gain coefficient

$$\Gamma = \frac{1}{1 + I_s/I} \left(\frac{A \sin \theta}{1 + B^{-2} \sin^2 \theta} \right) \left(\frac{\cos 2\theta'}{\cos \theta'} \right)$$

where

$$\begin{aligned} I_s &\propto \beta_w/s \\ A &\propto r_{eff} \\ B^2 &\propto N_{eff} \end{aligned}$$

Measured gain coefficient

$$g = \frac{I_{probe} (w / \text{pump})}{I_{probe} (w / o \text{ pump})}$$

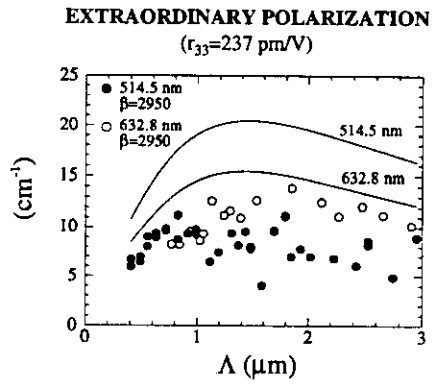
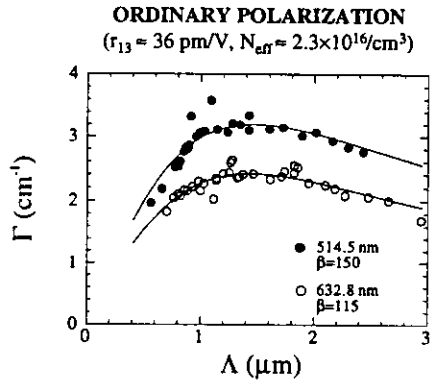
$$\Rightarrow \Gamma = \frac{1}{L} \ln \left(\frac{g\beta}{1 + \beta - g} \right)$$

Response rate

$$\begin{aligned} \tau^{-1} &= \frac{1}{\epsilon_0 \epsilon_s} (\sigma_{dark} + e\lambda\mu\tau_R I / hc) \\ &\times [1 + (2\pi L_D / \Lambda)^2] \end{aligned}$$

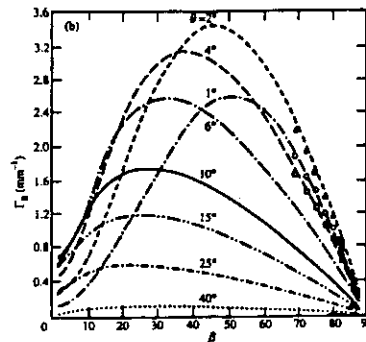
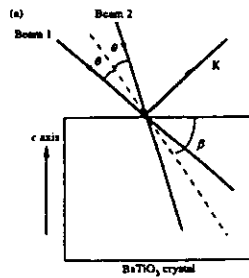
Experimental Results

– $\text{Sr}_{0.6}\text{Ba}_{0.4}\text{Nb}_2\text{O}_6:\text{Cr}$ (Cr-doped SBN:60)–



Tomita and Suzuki, Appl. Phys. A 59, 579 (1994)

Angular Dependence of Γ

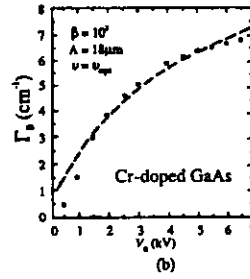
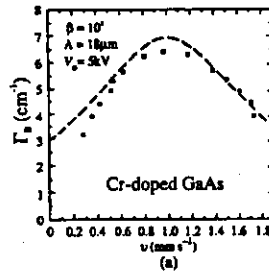
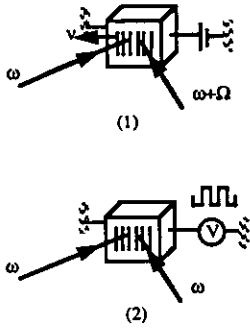


Fainman *et al.*, Opt. Eng. 25, 228 (1986)

Space-Charge Field and Gain Enhancement

Two Enhancement Techniques

- (1) Externally applied DC field with moving fringes
- (2) Externally applied AC field

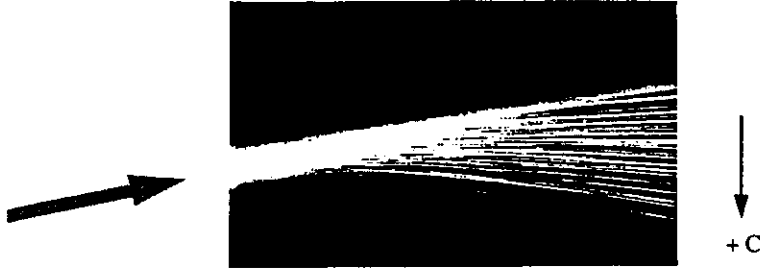


B. Imbert et al., Opt. Lett. 13, 327 (1988)

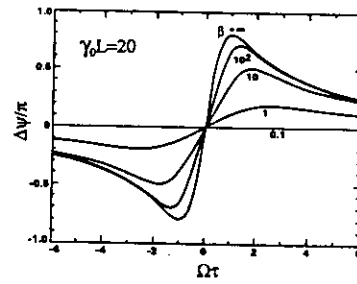
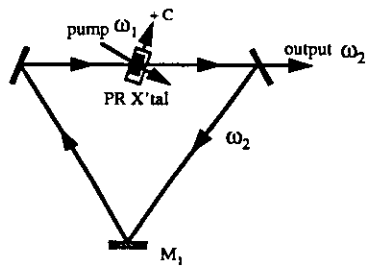
Beam Fanning Effect and Photorefractive Ring Oscillators

Beam Fanning Effect

If ΓL is too high (e.g., $\Gamma L = 20$),
then noise signals can be amplified by $\exp(20) \approx 5 \times 10^8$!



Unidirectional Ring Oscillator with Photorefractive Gain



P.Yeh, JOSA B2, 727(1985)

Oscillation Conditions

phase: $\Delta\psi = 2N\pi + (\text{cavity detuning phase})$

amplitude: $2\gamma_0 L > \alpha L - \ln R + 4(\Delta\psi)^2 (\alpha L - \ln R)^{-1}$

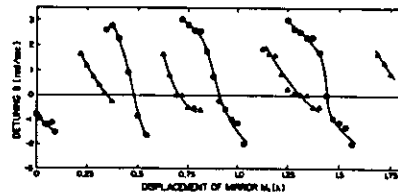
where

$$\gamma = \gamma_0 [1 + (\Omega\tau)^2]^{-1}$$

$$\gamma_0 = 2\pi n_1 / \lambda \cos\theta$$

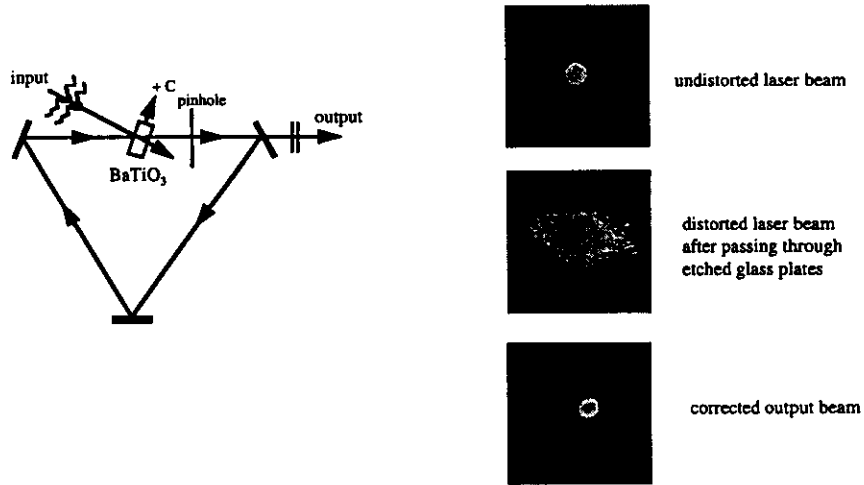
$$\Omega = \omega_2 - \omega_1$$

$$= 2\Delta\psi [\tau(\alpha L - \ln R)]^{-1}$$



S.K.Kwong *et al.*, JQE QE-22, 1508(1986)

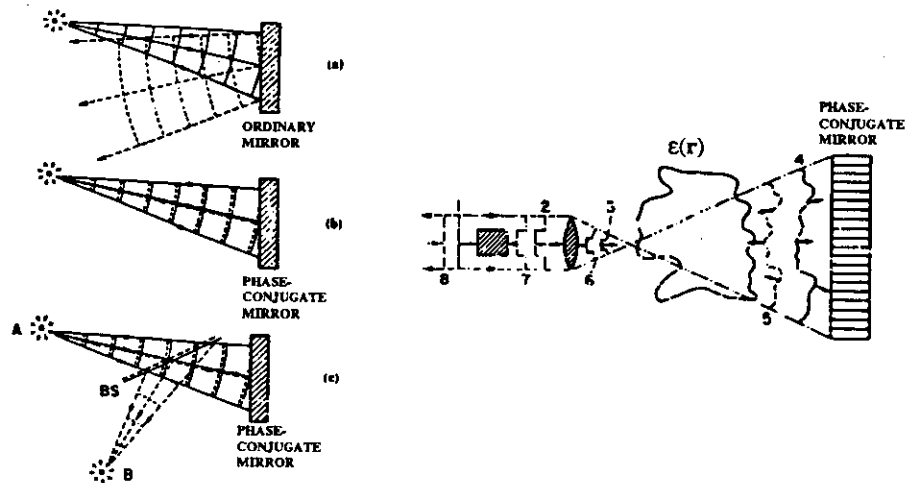
Application to one-way real-time wavefront converters



S.K.Kwong *et al.*, JQE QE-22, 1508(1986)

Optical Phase Conjugation and Photorefractive Four-Wave Mixing

Optical Phase Conjugation



Phase-Conjugate Waves

Input monochromatic wave

$$E_{\text{in}}(\mathbf{r}, t) = \text{Re}\{A(\mathbf{r}) \exp[i(\omega t - kz)]\}$$

$$= \text{Re}\{|A(\mathbf{r})| \exp[-i\phi(\mathbf{r})] \exp[i(\omega t - kz)]\}$$

Phase-conjugate wave

$$E_{\text{pc}}(\mathbf{r}, t) = \text{Re}\{[A(\mathbf{r}) \exp(-ikz)]^* \exp(i\omega t)\}$$

$$= \text{Re}\{A^*(\mathbf{r}) \exp[i(\omega t + kz)]\}$$

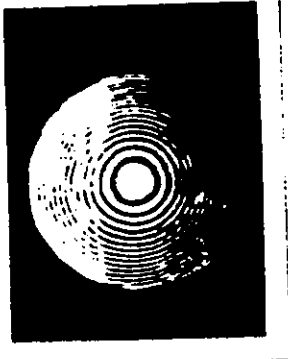
$$= \text{Re}\{|A(\mathbf{r})| \exp[i(\omega t + kz + \phi(\mathbf{r}))]\}$$

$$= \text{Re}\{|A(\mathbf{r})| \exp[i(-\omega t - kz - \phi(\mathbf{r}))]\}$$

$$= \text{Re}\{[A(\mathbf{r}) \exp(-ikz)] \exp[i\omega(-t)]\}$$

Time-reversed wave !

INTERFERENCE FRINGE PATTERNS



(a) without a glass plate



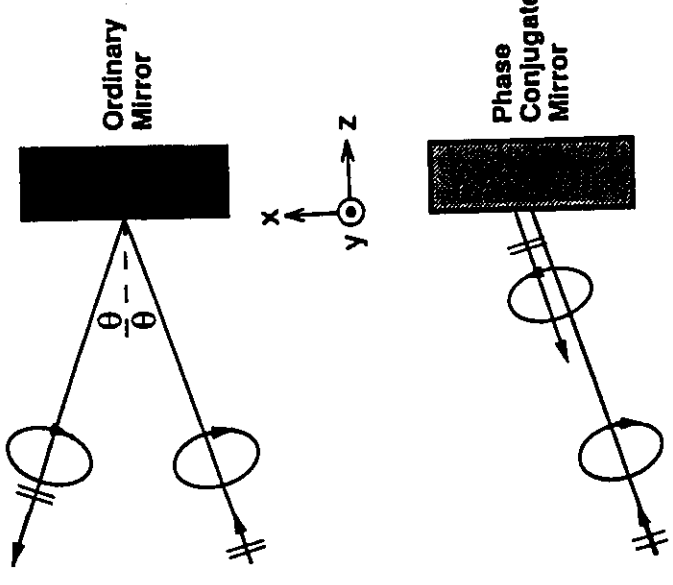
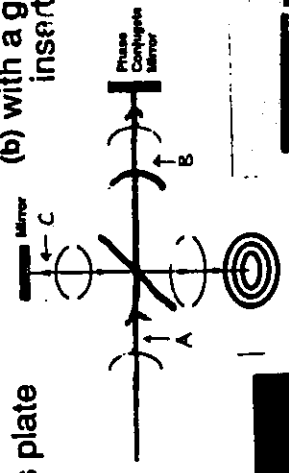
(b) with a glass plate inserted at A



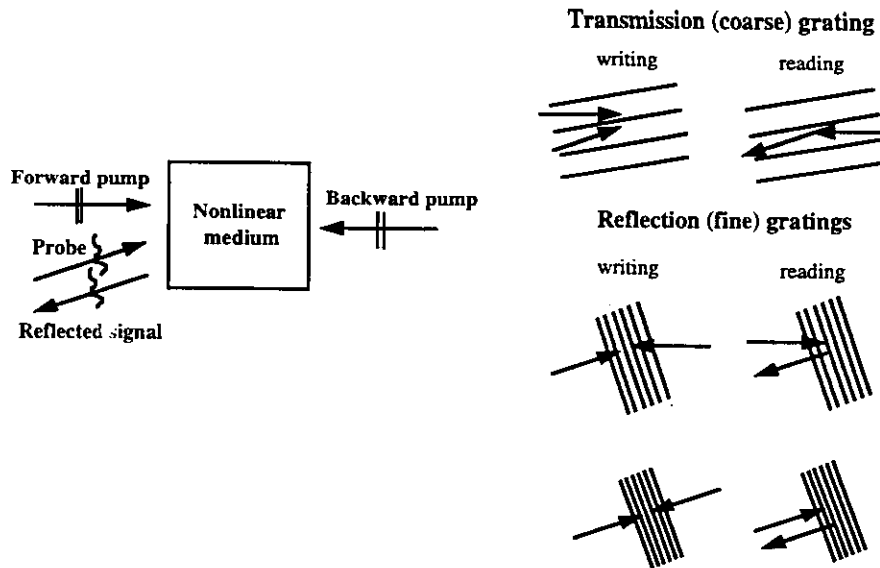
(c) with a glass plate inserted at B



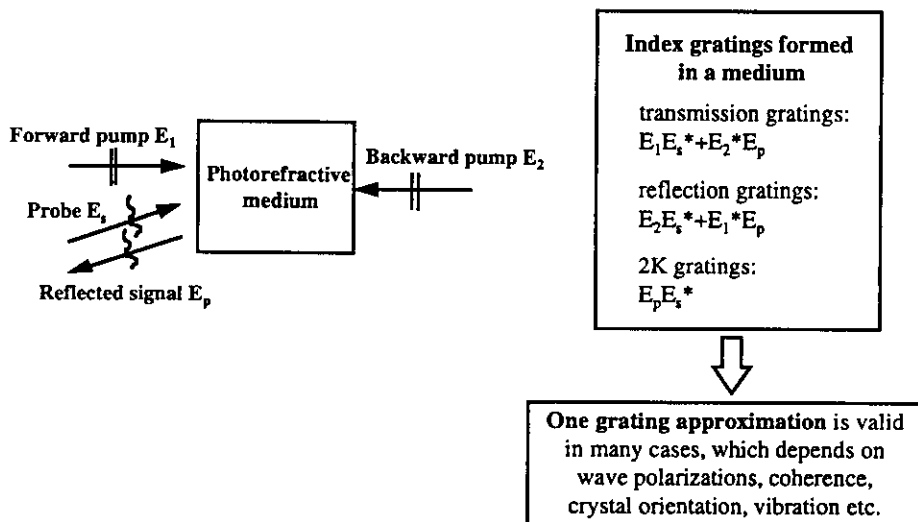
(d) with a glass plate inserted at C



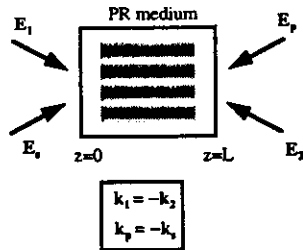
Optical Phase Conjugation by Four-Wave Mixing



Four-Wave Mixing in a Photorefractive Medium



Four-Wave Mixing with Transmission Gratings



$$\frac{dE_s}{dz} = -\gamma(E_s E_1^* + E_2 E_p^*) E_1 / I_0$$

$$\frac{dE_1}{dz} = \gamma^*(E_s^* E_1 + E_2^* E_p) E_s / I_0$$

$$\frac{dE_2}{dz} = \gamma(E_s E_1^* + E_2 E_p^*) E_p / I_0$$

$$\frac{dE_p}{dz} = -\gamma^*(E_s^* E_1 + E_2^* E_p) E_2 / I_0$$

where

$$I_0 = I_s + I_1 + I_2 + I_p$$

Constants of integration:

$$\left. \begin{aligned} |E_s|^2 + |E_1|^2 &= c_1 \\ |E_2|^2 + |E_p|^2 &= c_2 \end{aligned} \right\} \text{conservation of energy}$$

$$E_s E_p + E_1 E_2 = c_3 \quad \text{reciprocity}$$

Four-Wave Mixing with Transmission Gratings

Undepleted pump approximation: $|E_1|^2, |E_2|^2 \gg |E_s|^2, |E_p|^2 \Rightarrow dE_1/dz = dE_2/dz = 0$

$$\frac{dE_s}{dz} = -\gamma \frac{|E_1|^2}{I_0} E_s - \gamma \frac{E_1 E_2}{I_0} E_p^*$$

$$\frac{dE_p^*}{dz} = -\gamma \frac{|E_2|^2}{I_0} E_p^* - \gamma \frac{E_1^* E_2^*}{I_0} E_s$$

With $E_p(L) = 0$ and a given $E_s(0)$

$$E_s(z) = \frac{\exp(-\gamma z) + q \exp(-\gamma L)}{1 + q \exp(-\gamma L)} E_s(0)$$

$$E_p^*(z) = \frac{\exp(-\gamma z) - \exp(-\gamma L)}{1 + q \exp(-\gamma L)} \left(\frac{E_2^*}{E_1} \right) E_s(0) \Rightarrow E_p(0) \propto E_s^*(0)$$

where $q \equiv |E_2|^2 / |E_1|^2$

Phase - conjugate reflection coefficient

$$\rho \equiv \frac{E_p(0)}{E_s^*(0)}$$

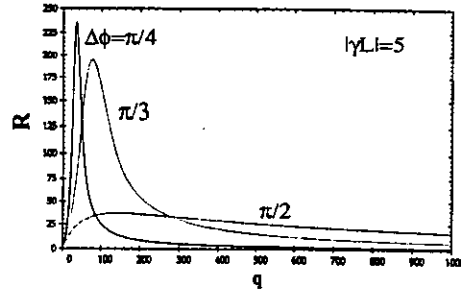
$$= \frac{1 - \exp(-\gamma^* L)}{1 + q \exp(-\gamma^* L)} \left(\frac{E_2}{E_1^*} \right)$$

Phase-Conjugate Reflectivity

PC reflectivity under one transmission
grating/undepleted pump approximations

$$R = \left| \frac{\sinh(\gamma L / 2)}{\cosh(\gamma L / 2 - \ln \sqrt{q})} \right|^2$$

where
 $\gamma = \gamma' + i\gamma''$
 $q = \text{pump int ensity ratio}$



Yeh, Introduction to NLO(1993)

i) diffusion operation ($\phi = \pi / 2$)

$$R_{\max} = \sinh^2(\Gamma L / 4) \quad \text{when } q_{\text{opt}} = \exp(\Gamma L / 2)$$

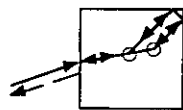
$$\Rightarrow R_{\max} \geq 100\% \text{ for } \Gamma L \geq 4 \ln(1 + \sqrt{2}) \approx 3.52 \quad \text{GAIN!}$$

ii) drift operation ($\phi \neq \pi / 2$)

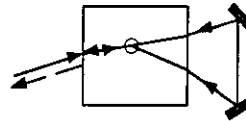
$$R_{\max} = \left| \frac{\sinh(\gamma L / 2)}{\cos(\gamma'' L / 2)} \right|^2 \quad \text{when } q_{\text{opt}} = \exp(\Gamma L / 2)$$

$$\Rightarrow R_{\max} \rightarrow \infty \text{ for } \gamma'' L = (2N - 1)\pi \quad \text{SELF OSCILLATION!}$$

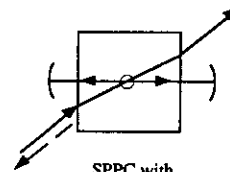
Self-Pumped Phase-Conjugate Mirrors (SPPCM's)



SPPC with
total internal reflection
(Cat SPPC)



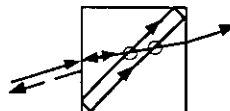
ring SPPC



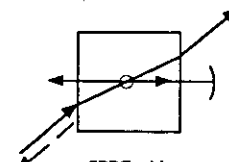
SPPC with
linear resonators



SPPC with
2K gratings



SPPC with
ring resonators



SPPC with
semi-linear resonators

SPPCM's

(a) Linear SPPC: $\gamma_{th}L = 0$

- self-starting
- critical to misalignment
- long coherence length

(b) Semi-linear SPPC: $\gamma_{th}L = 2.49$

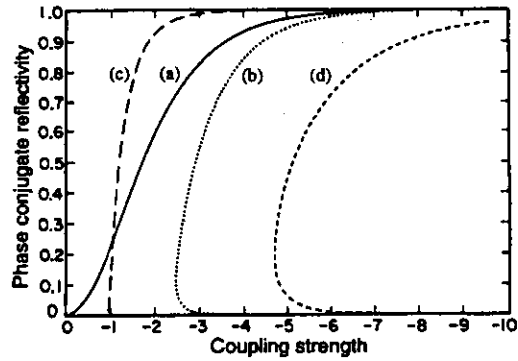
- can be self-starting
- critical to misalignment
- long coherence length

(c) Ring SPPC: $\gamma_{th}L = 1.0$

- can be self-starting easily
- robust against misalignment
- no coherence length requirement

(d) Cat SPPC: $\gamma_{th}L = 4.68$

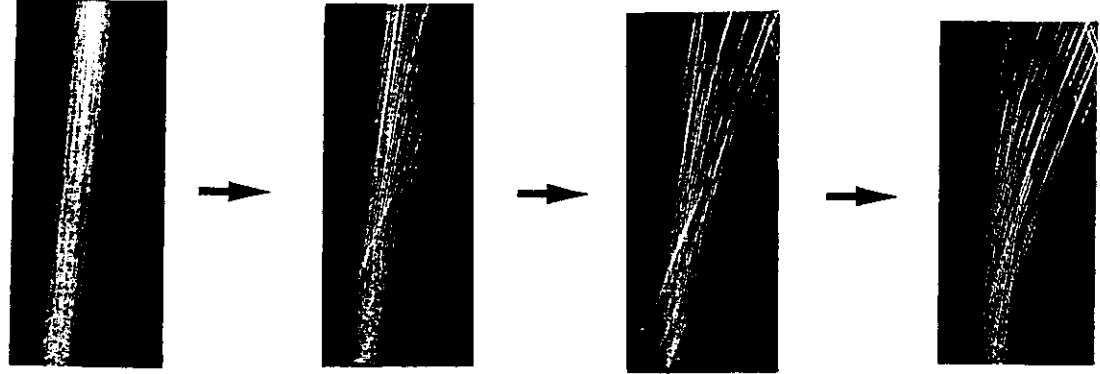
- can be self-starting
- robust against vibration
- short coherence length
- compact



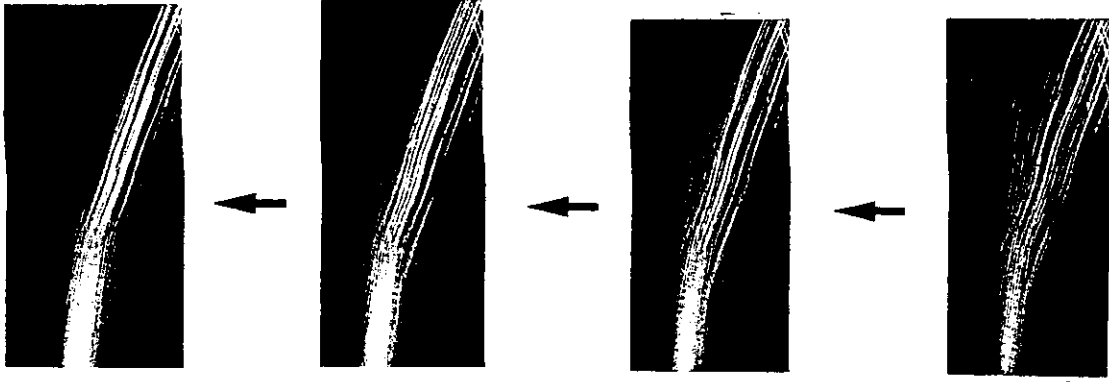
Cronin-Golomb et al., JQE 20, 12(1984)

DYNAMICS OF SELF-ORGANIZING PHASE CONJUGATION

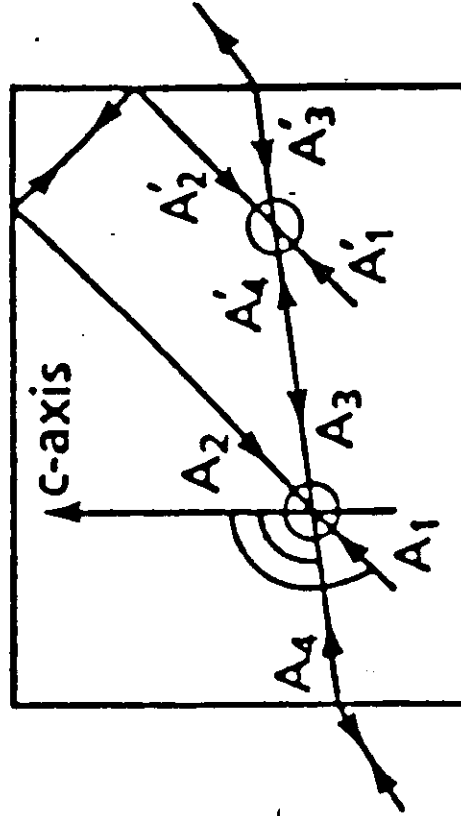
INITIAL STATE



STEADY STATE

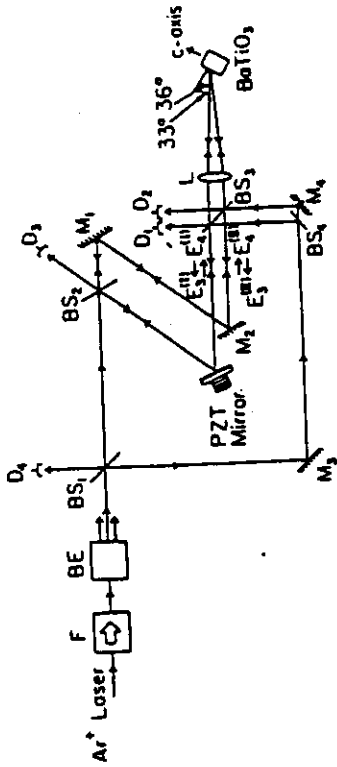


**SELF-PUMPED
PHASE-CONJUGATE MIRROR
USING INTERNAL REFLECTION**



$$P_3 \propto A_1 A_2 A_4^*$$

Phase shift of SPPCM



(Y. Tomita *et al.*, 1989)

Opt. Commun. 73, 118-119

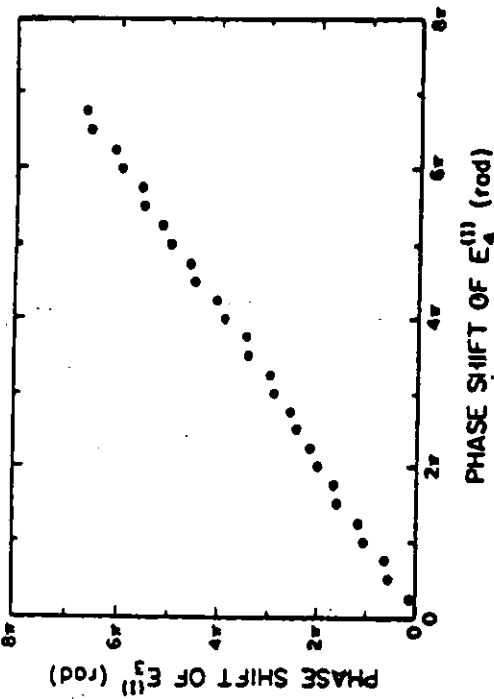


$$E_3 \propto E_1 E_2 E_4^*$$

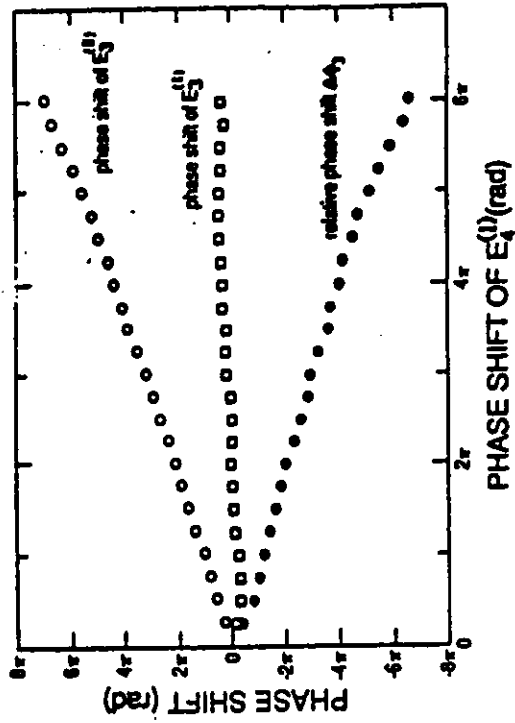
$$\phi_3 \propto \phi_1 + \phi_2 - \phi_4$$

$$\boxed{\phi_3 \rightarrow \phi_3 + \delta \text{ as } \phi_4 \rightarrow \phi_4 + \delta}$$

SINCE $\phi_{1,2} \rightarrow \phi_{1,2} + \delta$

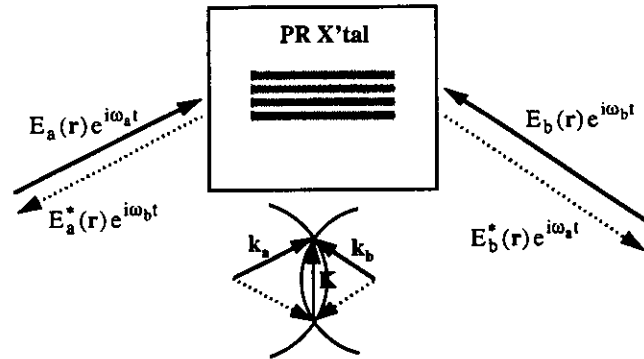


(a)



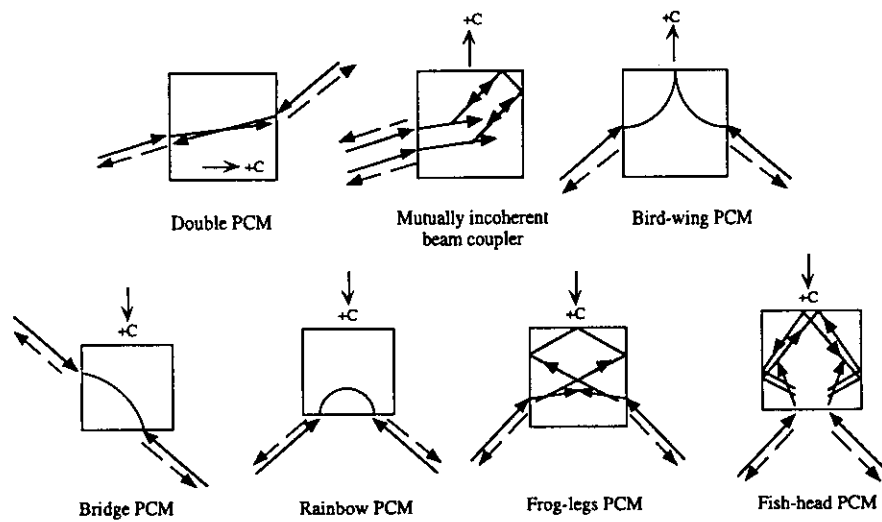
(b)

Mutually Pumped Phase-Conjugate Mirrors (MPPCM's)



- One phase-conjugate beam originates from the other input
- Two beams prefer to be mutually incoherent
- Wavefronts of input beams prefer to be spatially distorted

Several Configurations for MPPCM's



Proposed Models for MPPCM's

- **Self-Oscillation Model**
 - 1 interaction region (Cronin-Colomb *et al.*, 1984)
 - 2 interaction regions (He, 1988)
- **Resonator Model (Yeh *et al.*, 1988)**
- **Hologram Sharing Model (Ewbank, 1988)**

Photorefractive Materials
– figures of merit –

Steady-State Performance

i) Maximum change in the refractive index

$$\Delta n_{\max} = \frac{1}{2} n_b^3 r_{\text{eff}} E_{\text{sc}} \propto \begin{cases} n_b^3 r_{\text{eff}} & \text{(diffusion lim it)} \\ \frac{n_b^3 r_{\text{eff}}}{\epsilon_r} & \text{(trap lim it)} \end{cases}$$

ii) Response time of the space-charge field

$$\tau = \frac{\text{write or erase energy}}{\text{average int ensity}} = \tau_{\text{di}} \left(1 + \frac{4\pi^2 L_{\text{diff}}^2}{\Lambda^2} \right)$$

$$\approx \begin{cases} \frac{h\nu\epsilon}{\alpha q \mu \tau_R I_0} & \text{for } L_{\text{diff}} \ll \Lambda \text{ (ferroelectrics)} \\ \frac{4\pi^2 h\nu\epsilon k_B T}{\alpha q^2 \Lambda^2 I_0} & \text{for } L_{\text{diff}} \gg \Lambda \text{ (bulk semiconductors)} \end{cases}$$

where

τ_{di} = dielectric relaxation time

L_{diff} = diffusion length

I_0 = average int ensity

α = absorption coefficient

Transient-State Performance

Photorefractive sensitivity

– the index change per absorbed energy per unit volume

$$S = \frac{\Delta n}{\alpha I_0 \tau}$$

$$\rightarrow \begin{cases} \pi \mu \tau_R \left(\frac{n_b^3 r_{\text{eff}}}{\epsilon} \right) \left(\frac{k_B T}{\Lambda h\nu} \right) & \text{(diffusion lim it and } L_{\text{diff}} \ll \Lambda) \\ \frac{q}{4\pi} \left(\frac{n_b^3 r_{\text{eff}}}{\epsilon} \right) \left(\frac{\Lambda}{h\nu} \right) & \text{(diffusion lim it and } L_{\text{diff}} \gg \Lambda) \end{cases}$$

Figures of Merits for Photorefractive Materials

Materials	wavelength	ϵ/ϵ_0	σ_{dark} ($\Omega \cdot \text{cm}$) ⁻¹	$n^2 r_{eff}$ (pm/V)	$n^2 r_{eff}/\epsilon$ (pm/V ϵ_0)	τ at 1W/cm ² (sec)	S (cm ³ /J)
(ferroelectrics)							
LiNbO ₃	visible	32(ϵ_{33})	10 ⁻⁴ -10 ⁻¹⁹	330	10.3	>1	10 ⁻⁵
BaTiO ₃	visible	135(ϵ_{33})	10 ⁻¹²	1350	10	1	10 ⁻⁴
SBN:60	visible	880(ϵ_{33})	10 ⁻¹¹	2973	3.4	10	10 ⁻³
(paraelectrics)							
BSO	visible	56	10 ⁻¹⁵	82	1.5	10 ³	10 ⁻³
(semiconductors)							
GaAs	near IR	12.3	10 ⁻⁸	56	4.6	10 ⁻⁴	10 ⁻²
ZnTe:V	visible	10.1	10 ⁻⁹	133	13	10 ⁻⁴	10 ⁻²
Cr doped AlGaAs /GaAs MQW	near IR	-	10 ⁻⁹	-	-	10 ⁻⁵	10 ²
(polymers)							
PVK:TNF: DMNPAA	visible	-	-	-	-	10 ⁻¹	10 ⁻³

Photorefractive Materials – inorganic materials –

Ferroelectric Oxides

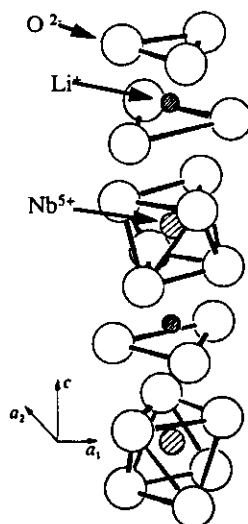
Typical materials exhibiting large photorefractivities

- Ilmenite structures (LiNbO_3 , LiTaO_3)
- Perovskite structures [BaTiO_3 , KNbO_3 , $\text{KTa}_{1-x}\text{Nb}_x\text{O}_3$ (KTN)]
- Tungsten-Bronze structures [$\text{Sr}_x\text{Ba}_{1-x}\text{Nb}_2\text{O}_6$ (SBN),
($\text{Ba}_{1-x}\text{Sr}_x$) $_{2-2\Delta}$ ($\text{K}_{1-y}\text{Na}_y$) $_{2\Delta-2}$ Nb_2O_6 (KNSBN)]

Several properties in common

- broadband photorefractive sensitivities (visible to near-infrared)
- large dielectric and electrooptic constants which are strongly temperature-dependent
- hard and nonhygroscopic materials (high-quality surfaces obtainable)

Lithium Niobate (LiNbO_3)



Structural phase transition

Trigonal $3m$ (ferroelectric) from R.T. to 1210°C

Impurity/defect levels

(deep levels)

$\text{Fe}^{2+}/\text{Fe}^{3+}$

$\text{Cu}^+/\text{Cu}^{2+}$

(shallow level)

intrinsic defect Nb_{Li} (small polaron, Nb^{4+} on Li^+ site)

Photorefractive effect

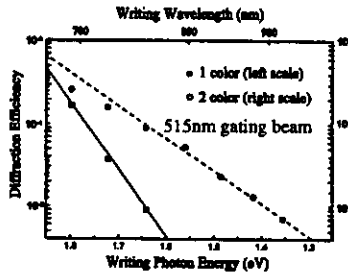
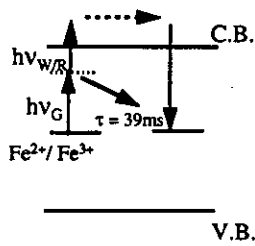
(main transport mechanism)

bulk photovoltaic effect / one-center model valid

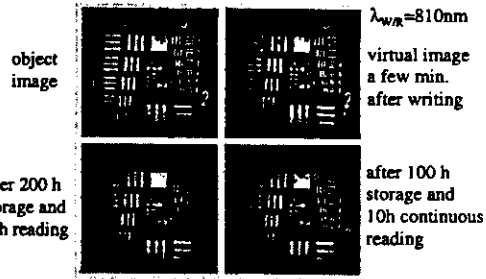
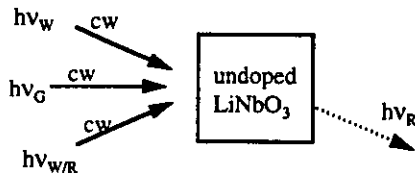
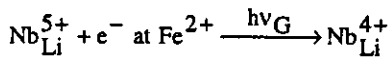
(dominant charge carriers)

electrons (holes when oxidized)

Nonvolatile Holographic Storage with Two-Color Hologram Recording in LiNbO₃

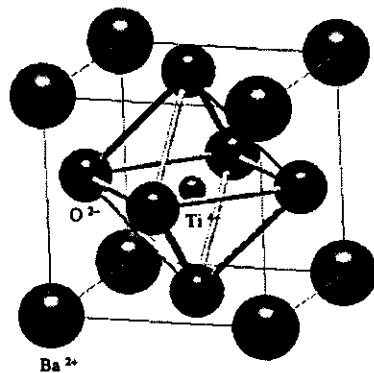


(Sensitization)



Bai and Kachru, PRL 78, 2944 (1997)

Barium Titanate (BaTiO₃)



Structural phase transitions

- T ≥ 130 °C: cubic *m3m* (paraelectric)
- 7 °C ≤ T ≤ 130 °C: tetragonal *4mm* (ferroelectric)
- 90 °C ≤ T ≤ 7 °C: orthorhombic *mm2* (ferroelectric)

Impurity/defect levels

- (deep levels)
- Fe²⁺/Fe³⁺
- Fe³⁺/Fe⁴⁺
- Ba²⁺ vacancy
- (shallow levels)
- O²⁻ vacancy
- Ba²⁺ vacancy

The Photorefractive Effect in BaTiO₃

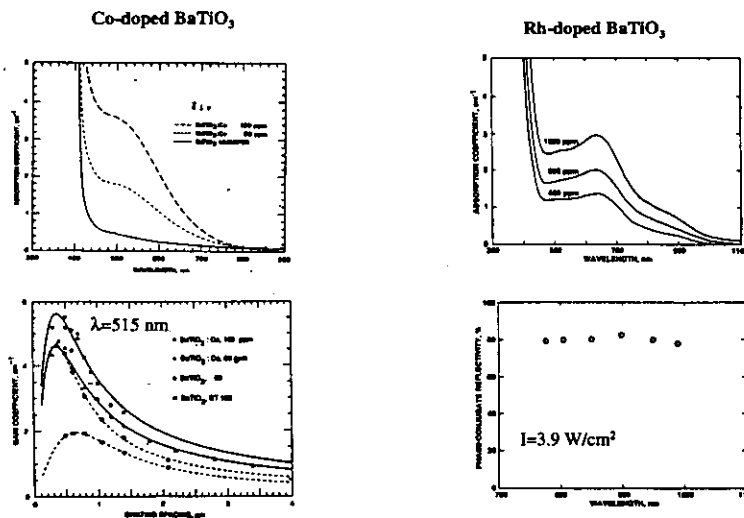
Main characteristics

- existence of shallow levels
 - intensity-dependent absorption
 - semi-linear intensity dependence of response time
- increased photorefractivities in visible and near-infrared spectra by doping with cobalt or rhodium

Impurity/defect levels responsible for the PR effect

	PR carriers	major deep levels	shallow levels
As-grown BaTiO ₃ reduced BaTiO ₃	holes electrons	Fe ³⁺ /Fe ⁴⁺ , Ba ²⁺ vacancy	Fe ⁴⁺ /Fe ⁵⁺ , O ²⁻ vacancy
Co-doped BaTiO ₃	holes	Co ²⁺ /Co ³⁺ , Fe ³⁺ /Fe ⁴⁺	Fe ⁴⁺ /Fe ⁵⁺ ,
Rh-doped BaTiO ₃	holes	Rh ³⁺ /Rh ⁴⁺ , Fe ³⁺ /Fe ⁴⁺	Rh ⁴⁺ /Rh ⁵⁺ , Fe ⁴⁺ /Fe ⁵⁺

Photorefractive Properties of Doped BaTiO₃

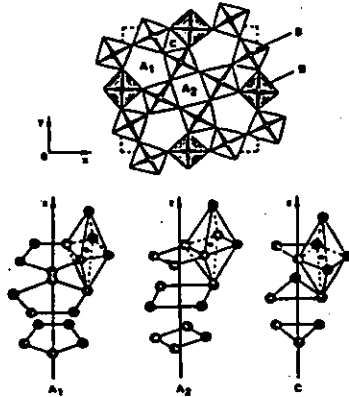


(Rytz *et al.*, 1990)

(Wechsler *et al.*, 1994)

Strontium Barium Niobate (SBN) and Potassium Sodium Strontium Barium Niobate (KNSBN)

Projection of structure of tetragonal ($4mm$) tungsten bronze parallel to (001)



A₁:15-fold; A₂:12-fold; C:9-fold; B:6-fold coordinated sites

Unique Advantages

- extraordinarily large electrooptic coefficients
- structural flexibility due to partially empty sites
- no phase transition at low temperatures
- large size available due to the absence of 90° twins

List of Typical PR Materials belong to $(A_1)_4(A_2)_2B_{10}O_{30}$

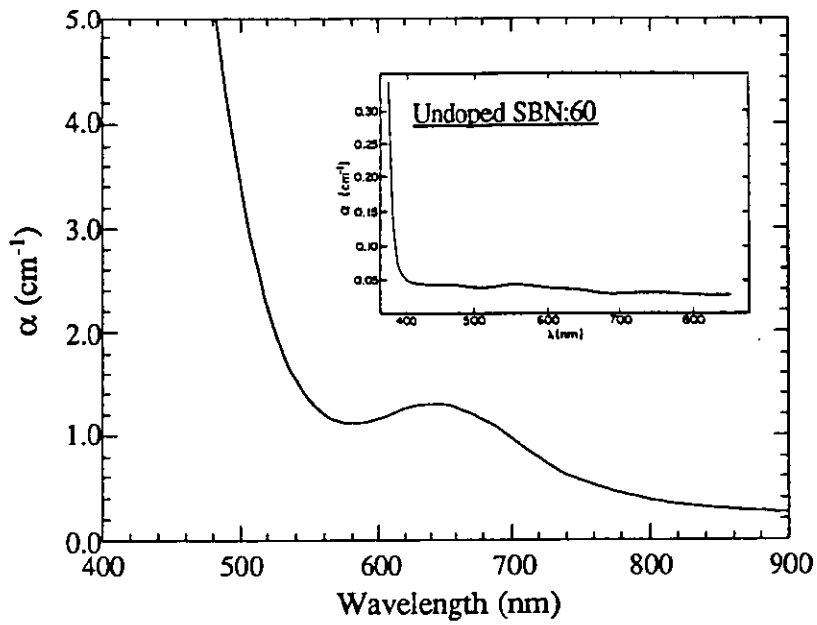
composition	r (pm/V)	T _c (°C)	partially empty sites
Sr _x Ba _{1-x} Nb ₂ O ₆			
SBN:60 (x=0.6)	235(r ₃₃)	75	15- and 12-fold sites up to 20%
SBN:75 (x=0.75)	1340(r ₃₃)	56	
KNSBN	270 (r ₃₃) 400 (r ₄₂)	71	15- and 12-fold sites

Comparison of Photorefractive BaTiO₃, SBN and KNSBN

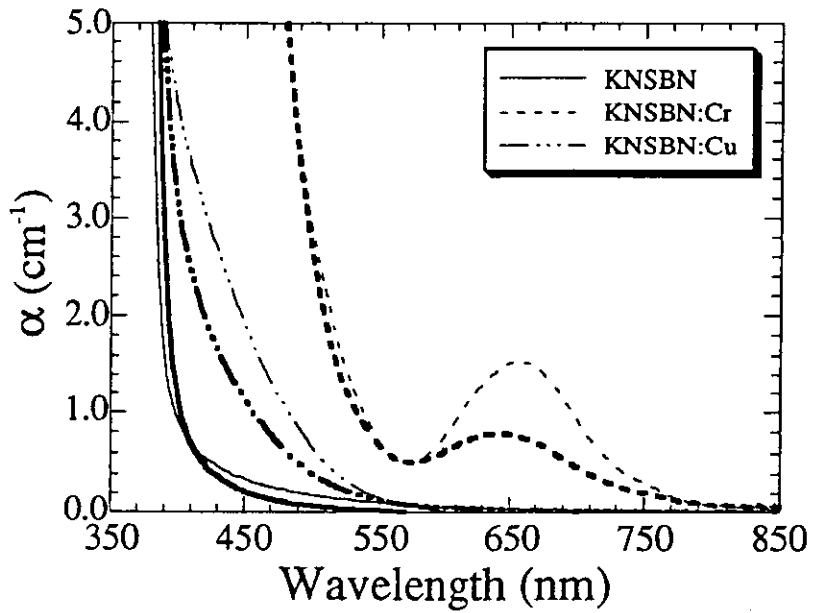
CRYSTAL	SBN, KNSBN	BaTiO ₃
STRUCTURE	TUNGSTEN-BRONZE	PEROVSKITE
GROWN IN LARGE SIZE	RELATIVELY EASY	DIFFICULT
ε	LARGE ε ₃₃ (SBN), ε ₁₁ (KNSBN)	LARGE ε ₁₁ , ε ₃₃
r	LARGE r ₃₃ (SBN), r ₅₁ (KNSBN)	LARGE r ₅₁
COMPOSITIONS CHANGE	EASY	DIFFICULT
DOPING	EASY	DIFFICULT
PHASE TRANSITION POINT BELOW R.T.	NO	NEAR 5°C

ABSORPTION SPECTRA

Cr-doped (0.02 wt.%) SBN:60

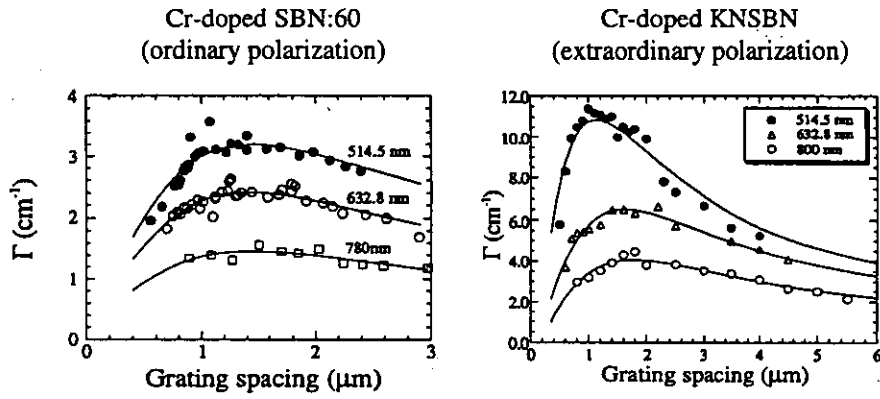


KNSBN



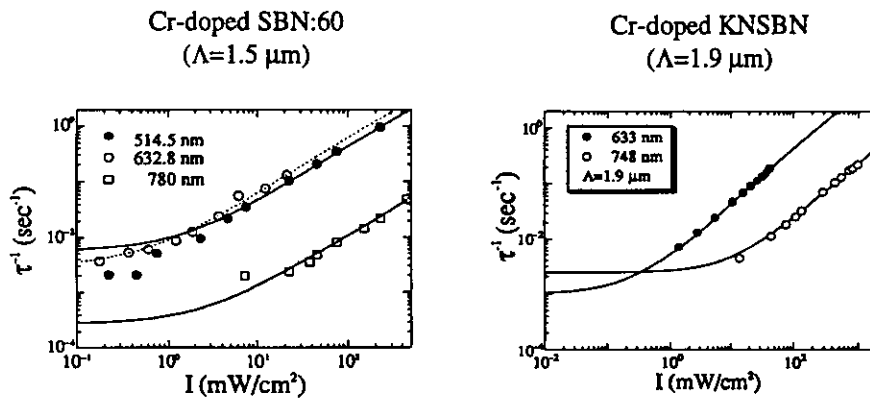
* extraordinary light (bold curves)

Grating Spacing Dependence of Γ



Y. Tomita and A. Suzuki, Opt. Rev. 1, 233 (1994)

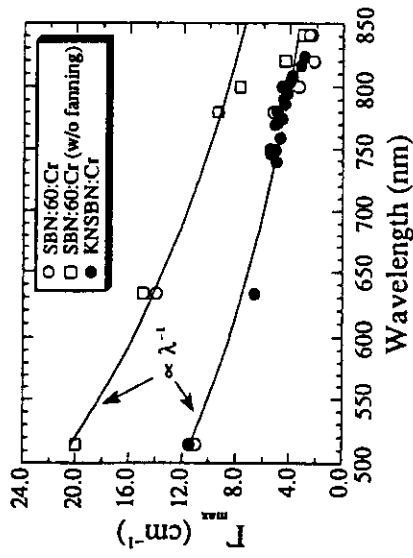
Intensity Dependence of Response Rate



Y. Tomita and A. Suzuki, Opt. Rev. 1, 233 (1994)

PHOTOREFRACTIVE SPECTRA

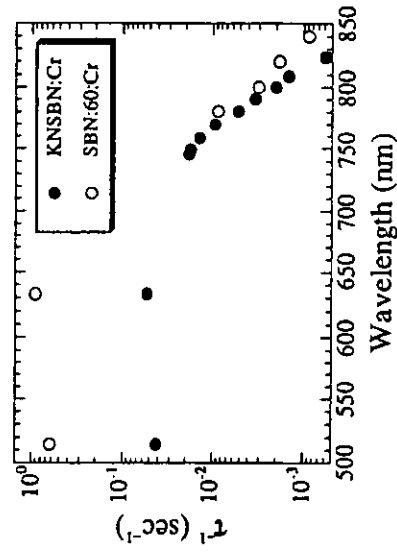
MAXIMUM Γ



31

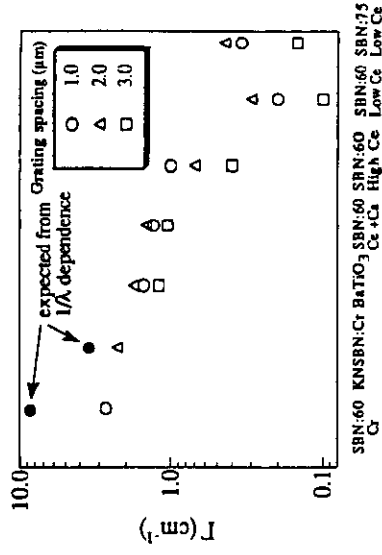
RESPONSE RATE

($I=150\text{mW/cm}^2$ and $\Lambda=1.5\mu\text{m}$)

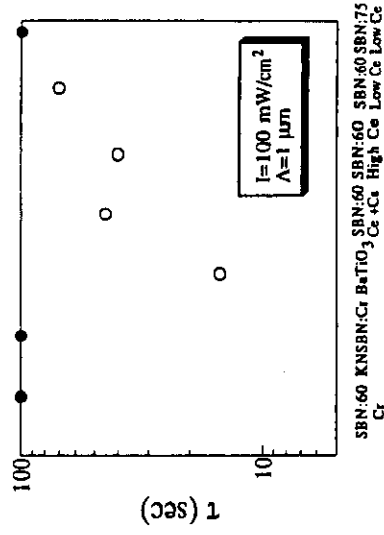


COMPARISON WITH OTHER DOPED CRYSTALS (@ $\lambda=840\text{nm}$)

GAIN COEFFICIENT



RESPONSE TIME



* other data are taken from G.A.Rakuljic, Ph.D. thesis, (Caltech,1987)

TEMPERATURE DEPENDENCE OF Γ (KNSBN:Cr @ $\lambda=632.8$ nm)

RELATIONSHIP BETWEEN Γ AND ϵ

$$\Gamma = 2g\epsilon_0\epsilon_s P_s$$

WHERE g : 2ND-ORDER EO COEFFICIENT
 P_s : SPONTANEOUS POLARIZATION

$$\begin{pmatrix} I_{13} = 2g_{13}\epsilon_0\epsilon_{33}P_s \\ I_{33} = 2g_{33}\epsilon_0\epsilon_{33}P_s \\ I_{42} = 2g_{44}\epsilon_0\epsilon_{11}P_s \end{pmatrix}$$

POWER-LAW DEPENDENCE

$$\epsilon_s \propto (T_c - T)^{-\gamma} \rightarrow \Gamma \propto (T_c - T)^{\delta-\gamma}$$

$$P_s \propto (T_c - T)^\delta$$

SCALING LAW OF Γ

$$\Gamma = \frac{Q_1}{\Lambda} \frac{T(T_c - T)^\delta}{(T_c - T)^\gamma + Q_2 T / \Lambda^2}$$

$$\Gamma_{\max} \propto (T_c - T)^{\delta-0.5\gamma}\sqrt{T}$$

$$\Lambda_{\text{opt}} \propto (T_c - T)^{-0.5\gamma}\sqrt{T}$$

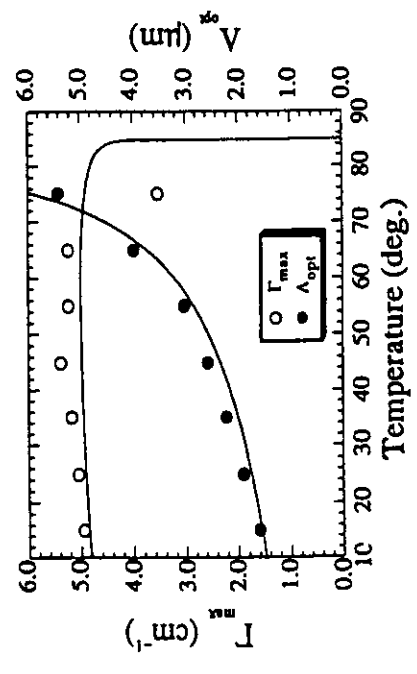
SO

SCALING LAW OF τ^{-1}

$$\tau^{-1} \propto (T_c - T)^\gamma + Q_2 T / \Lambda^2$$

$$T_c = 84.8^\circ \text{C}, \delta = 0.67, \gamma = 1.256$$

$$\Gamma_{0\max} \propto (T_c - T)^{\delta-0.5\gamma}\sqrt{T} \quad \Lambda_{\text{opt}} \propto (T_c - T)^{-0.5\gamma}\sqrt{T}$$



Y. Tomita (1985)

Opt. Materials 4, 281-288 (1985)

Photorefractive Materials – semi-insulating semiconductors–

Photorefractive Semiconductors

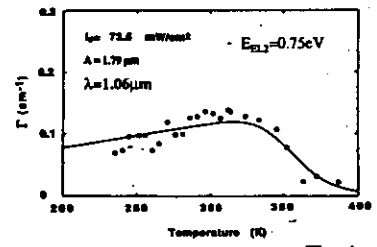
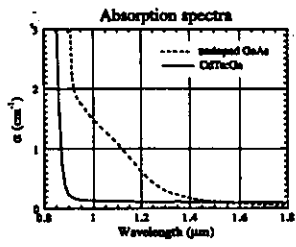
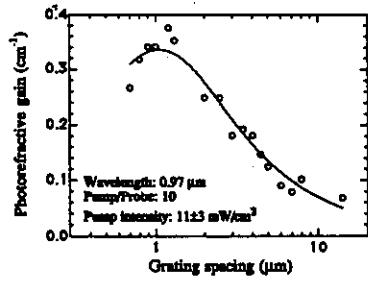
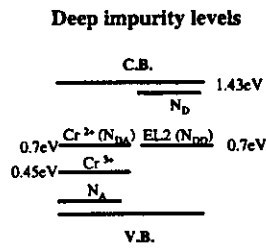
Typical PR semiconductors/structures

- **Bulk SI semiconductors**
 - undoped GaAs and GaAs:Cr
 - InP:Fe
 - CdTe:V
 - CdMnTe
 - GaP
- **SI Quantum-well/supperlattice structures**
 - GaAs/AlGaAs
 - ZnTe/CdZnTe

Major electrooptic phenomena in PR semiconductors/structures

- **Pockels effect**
- **quadratic electrooptic effect via band-edge Franz-Keldysh and quantum-confined Stark/Franz-Keldysh effects**
- **high field effect**
- **picosecond PR effect**

Undoped GaAs

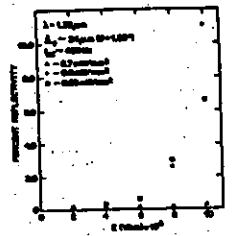


(Tomita *et al.*, 1989)

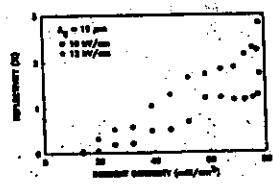
SPPCM and DPCM Using PR Semiconductors

SPPCM

- InP:Fe at 1.32 μm (Bylsma *et al.*, 1989)

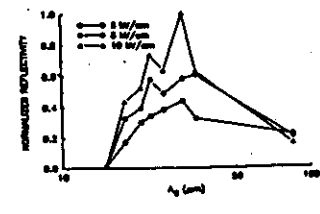


- Undoped GaAs at 1.06 μm (Chua *et al.*, 1990)

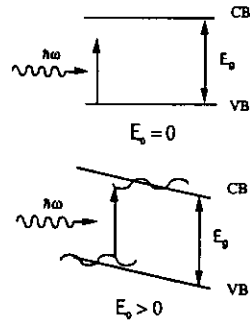


DPCM

- Undoped GaAs at 1.06 μm (Chua *et al.*, 1990)



Band-Edge Photorefractive Effect

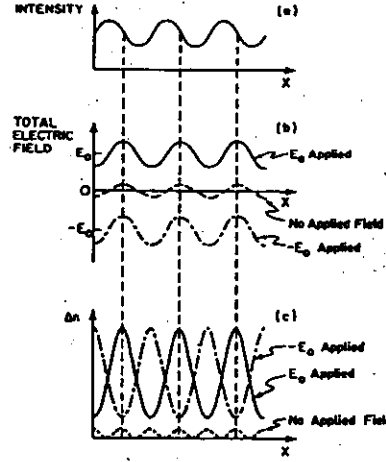


$$\alpha \rightarrow \alpha + \Delta\alpha(E_{\text{total}}) \Rightarrow n \rightarrow n + \Delta n(E_{\text{total}})$$

where

$$\Delta n(E_{\text{total}}) = AE_{\text{total}}(x) + BE_{\text{total}}^2(x)$$

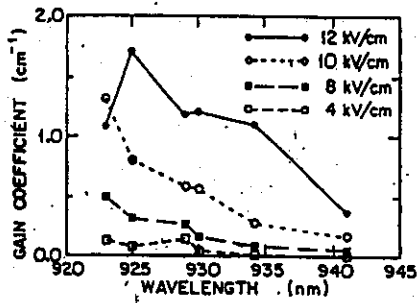
$$E_{\text{total}}(x) = E_0 + E_{\text{sc}}(x)$$



(Partovi et al., 1990)

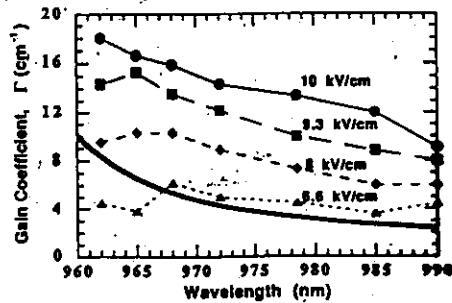
Band-Edge Photorefractive Effect – experimental results –

Undoped GaAs



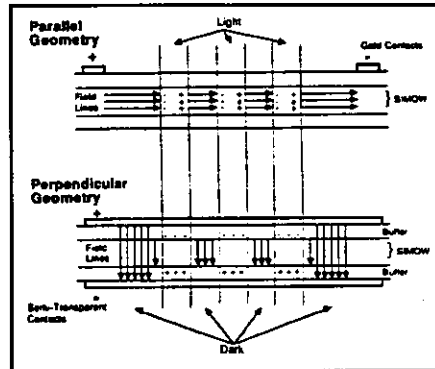
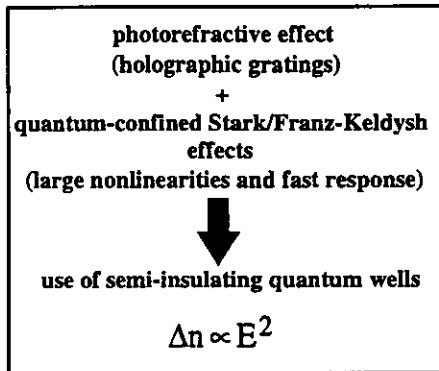
(Partovi et al., 1990)

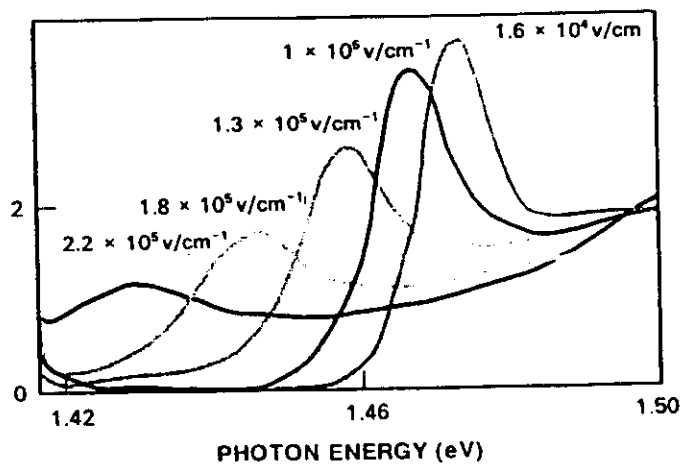
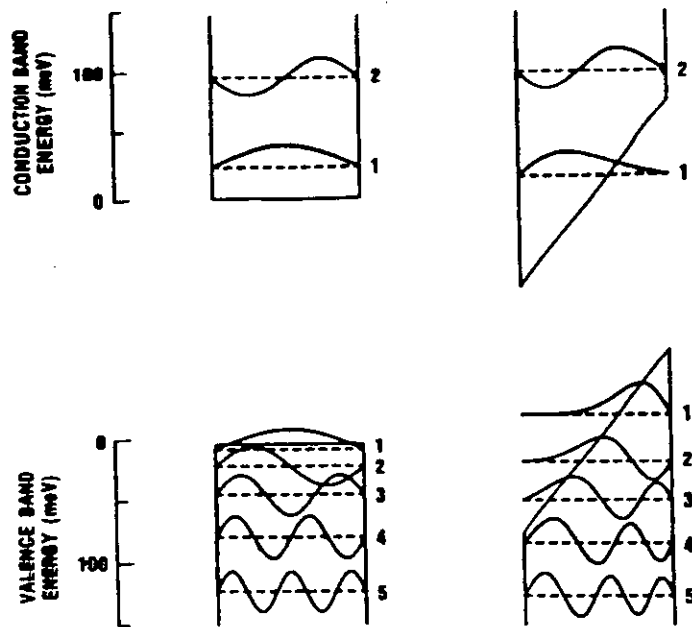
InP:Fe



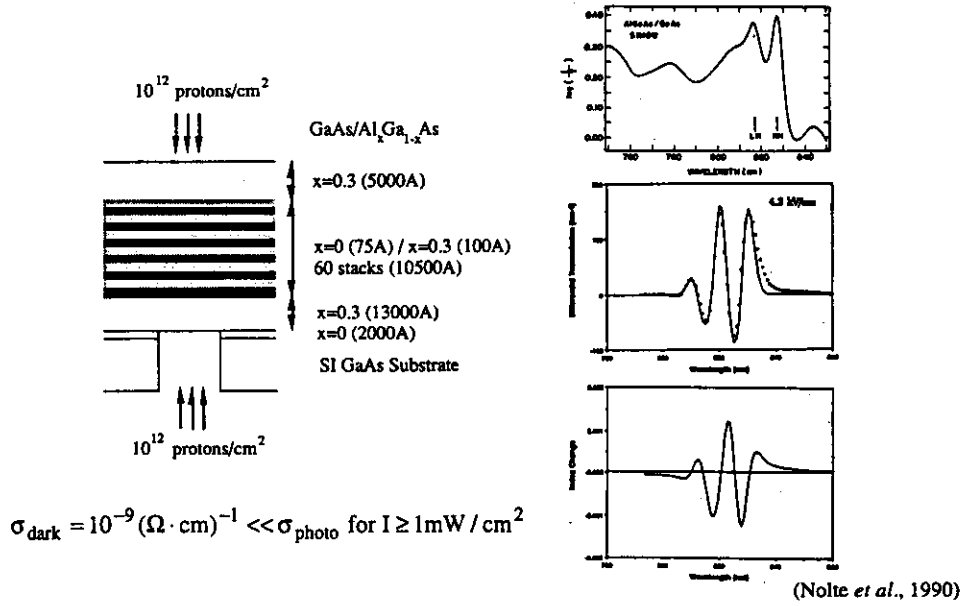
(Miller et al., 1990)

Resonant Photorefractive Effect in Semi-Insulating Quantum Wells

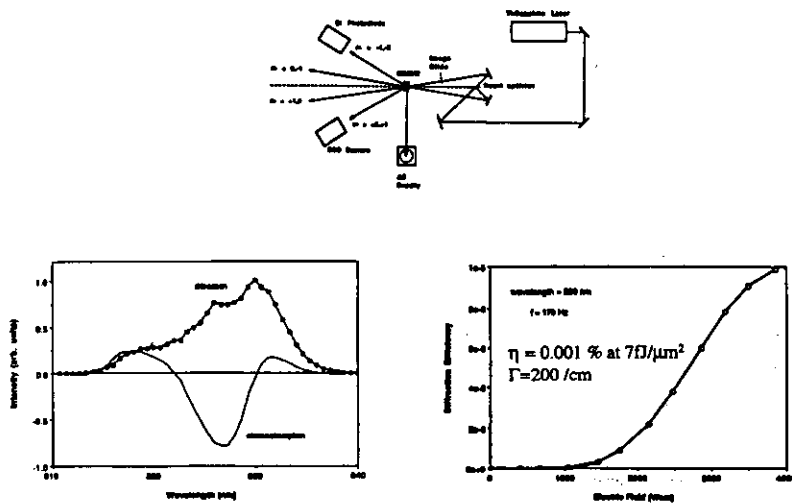




Photorefractive GaAs/AlGaAs Quantum Wells (parallel geometry)



Diffraction Efficiencies of photorefractive GaAs/AlGaAs Quantum Wells



Advantages of Photorefractive GaAs/AlGaAs Quantum Wells

- low saturation intensity I_{sat}

$$I_{sat} = \frac{h\omega\sigma_{dark}}{e\mu\tau_R\alpha} = 100 \text{ nW/cm}^2 \approx \frac{I_{sat}(\text{bulk})}{10000}$$

- fast response τ

$$\tau = \tau_{di} \left[1 + \left(\frac{2\pi\mu\tau_R E}{\Lambda} \right)^2 \right] = 100 \mu\text{sec} = \frac{\tau(\text{bulk})}{10000}$$

for $I = 100 \text{ mW/cm}^2$ and $E = 10^4 \text{ V/cm}$

- low switching energy E_{sw}

$$E_{sw} = I\tau = 155 \text{ fJ}/\mu\text{m}^2 \text{ for } E = 10^4 \text{ V/cm}$$

- high PR sensitivity S

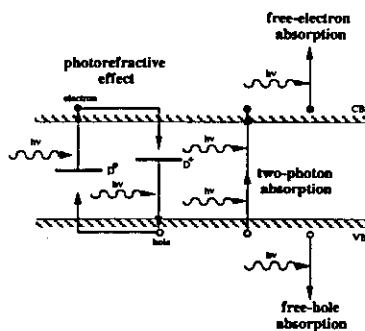
$$S = \frac{\Delta n_{\text{resonance}}}{\alpha I \tau} \leq 10^{-2} \text{ cm}^3/\text{J} \approx 10^4 S(\text{bulk})$$

- large refractive index changes $\Delta n_{\text{resonance}}$

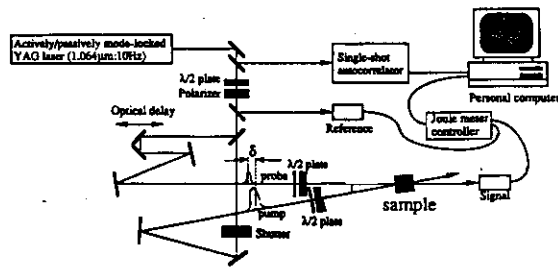
$$\begin{aligned} \Delta n_{\text{resonance}} &\approx 2\Delta n(\text{bulk})E(\text{cm/V}) \\ &= 10^4 \Delta n(\text{bulk}) \text{ at } E = 5 \text{ kV/cm} \end{aligned}$$

These advantages can be attributed mainly to large quadratic electrooptic effects and large linear absorption.

Picosecond Photorefractive Effect



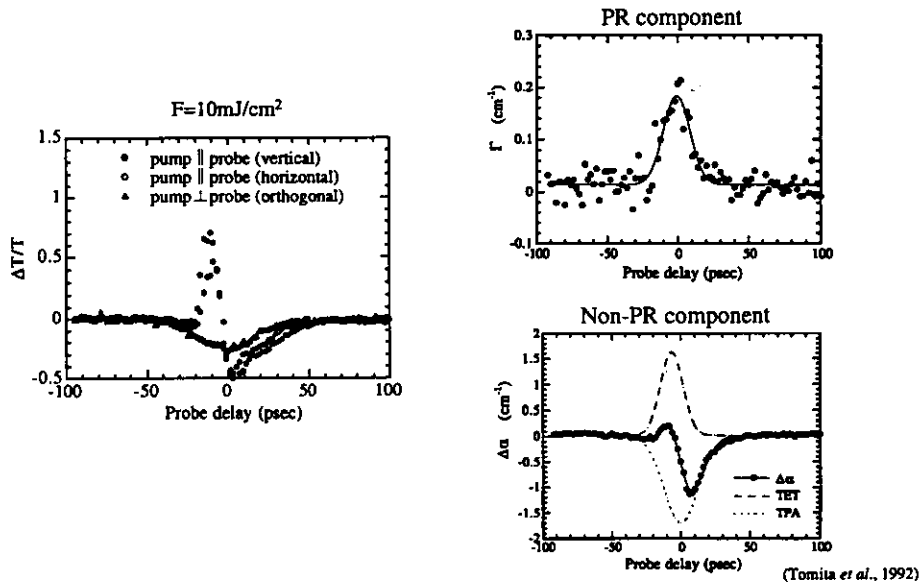
Experimental setup for picosecond beam coupling



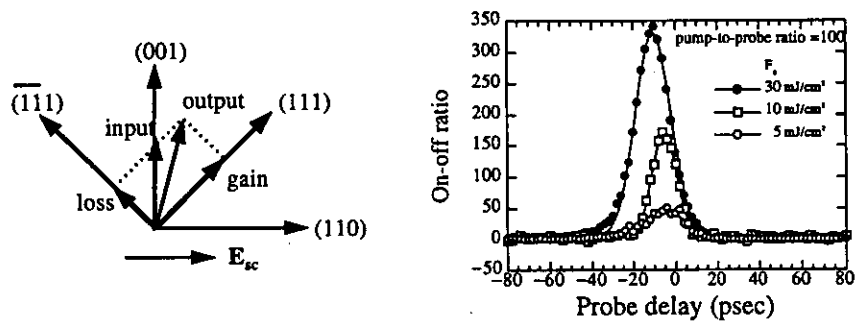
Nonlinear transmit tan ce change

$$\Delta T = \frac{T(w/\text{pump}) - T(w/\text{o pump})}{T(w/\text{o pump})}$$

Picosecond Photorefractive Effect in Undoped GaAs



Picosecond Polarization Switching Using SI CdTe:Ga

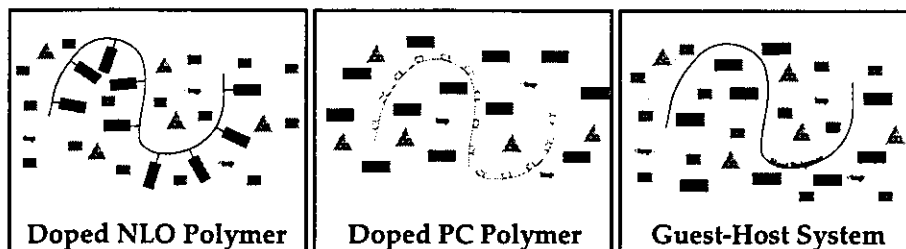


Tomita and Enami., APL 66,914(1995)

Photorefractive Materials – organic materials –

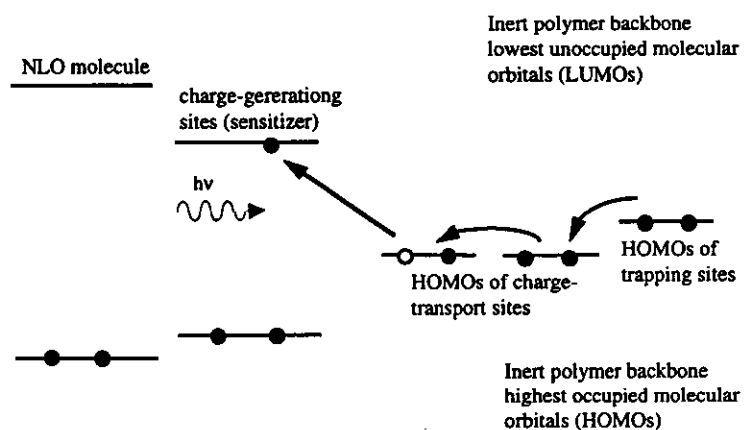
Photorefractive Polymers

- First reported by Ducharme et al.*
- Incorporate charge-generation materials, charge-transfer materials, and NLO entities
- Three families of polymeric PR materials



*S. Ducharme, J.C. Scott, R.J. Twieg, and W.E. Moerner, Phys. Rev. Lett. 66, 1846-49 (1991).

Space-Charge Field Formation Process in a Photorefractive Polymer



Reported Material Systems for Photorefractive Polymers

Material System	λ (nm)	η_{diff}	Γ_{2BC} (cm ⁻¹)	Type
bis-A-NPDA:DEH	647	5×10^{-5}	0.33	NLO
PMMA-PNA:DEH:C ₆₀	647	4.8×10^{-5}	0.6	NLO
PVK:TNF:EPNA	633	2×10^{-3}	18	PC
PVK:TNF:DMNPAA:ECz	675	8.6×10^{-1}	207	PC
PVK:TNF:DRI:ECz	700	1.6×10^{-5}	---	PC
PBPES:TNF:FDEAMNST	676	1.3×10^{-2}	9.9	PC
PMMA:DEH:NPP:SQ	633	1.1×10^{-2}	10	G-H

*NLO = NLO polymer; PC = photoconducting polymer; G-H = guest-host system

Main Characteristics of Photorefractive Polymers

1. Application of external field:

a) Poling for NLO

b) Photoconduction:

carrier generation

carrier mobility



function of externally applied field (E_0)

2. Orientation enhancement effect†

- Enhancement of PR effect due to modulated birefringence

†W.E. Moerner, S.M. Silence, F. Hache, and G.C. Bjorklund, J. Opt. Soc. Am. B 11, 320-30 (1994)

Orientation Enhancement Effect in Low-Glass Transition Temperature Photorefractive Polymers

NL chromophores are aligned according to the total poling field given by

$$E_{\text{total}}(\mathbf{r}) = E_0 + E_{\text{sc}}(\mathbf{r})$$

$$= [E_{\text{sc}}(\mathbf{r}) \sin \theta] \mathbf{e}_x + [E_0 + E_{\text{sc}}(\mathbf{r}) \cos \theta] \mathbf{e}_z$$

Orientalional birefringence contribution

$$\Delta n_{\text{BR}}^s \propto -N\mu^2 \Delta\alpha E_0 E_{\text{sc}}$$

$$\Delta n_{\text{BR}}^p \propto N\mu^2 \Delta\alpha E_0 E_{\text{sc}}$$

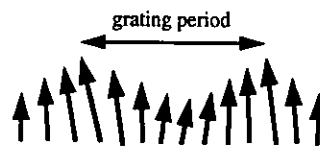
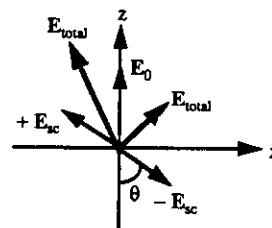
where

$$\Delta\alpha = \alpha_{\parallel} - \alpha_{\perp}$$

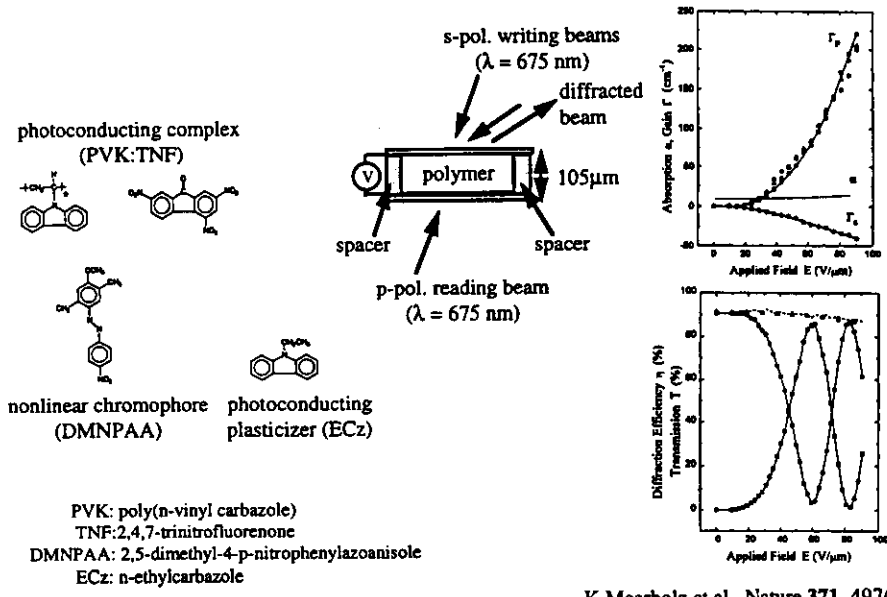
Electrooptic contribution

$$\Delta n_{\text{EO}}^s \propto N\mu\beta E_0 E_{\text{sc}}$$

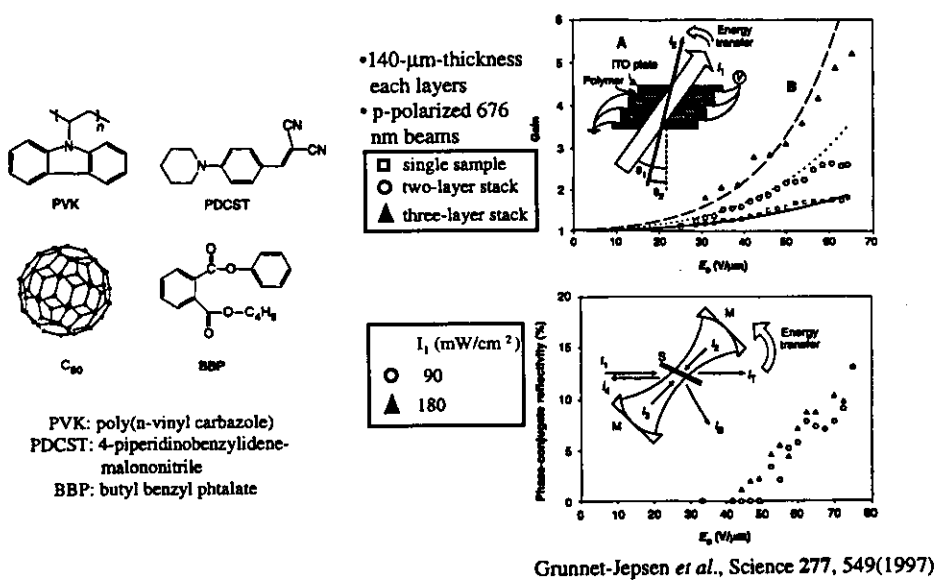
$$\Delta n_{\text{BR}}^p \propto N\mu\beta E_0 E_{\text{sc}}$$



PVK:TNF:DMNPAA:ECz



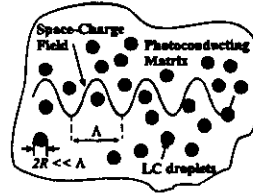
Self-Pumped Phase Conjugation with Photorefractive Polymer Stacks



Photorefractive Polymer-Dispersed Liquid Crystals

Main advantages

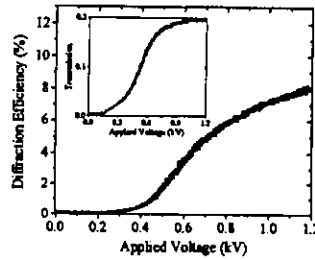
- high index changes with much lower electric fields (a few V/cm)
- high resolution of photorefractive polymers



PMMA:E49:TNF:ECz
 $\langle 2R \rangle = 0.25 \mu\text{m}$
 sample thickness = 53 μm

torque induced by $E_0 + E_{sc}$ = elastic torque

➔ $\Delta n \propto E_0 E_{sc}$



$\lambda_{\text{write}} = 633 \text{ nm}$ (1mW)
 $\lambda_{\text{read}} = 675 \text{ nm}$ (10 μW)

No higher-order diffraction



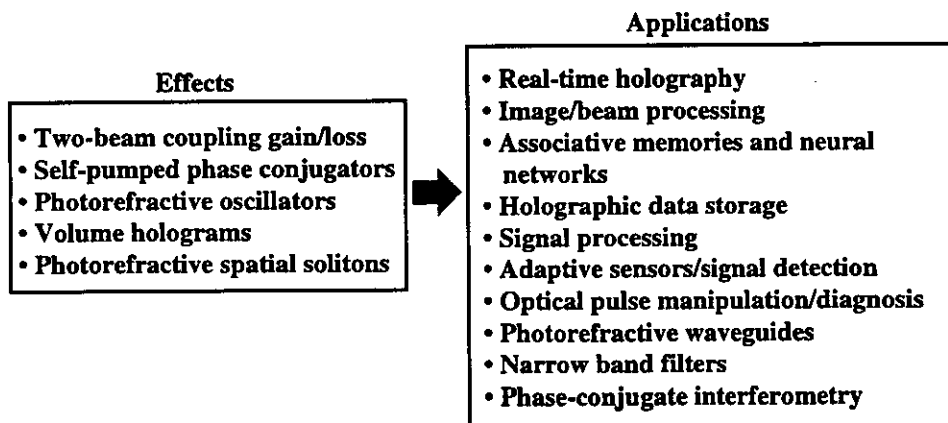
Bragg diffraction regime

$\Delta n = 2 \times 10^{-3}$ at 1.2 kV
 $\Gamma = 41 / \text{cm}$ ($\alpha = 735 / \text{cm}$)
 at 0.3 kV

A. Golemme *et al.*, Opt. Lett. **22**,1226(1997)

Applications

Possible Applications of Photorefractive Nonlinearities



Applications of Two-Beam Coupling to Image/Beam Processing

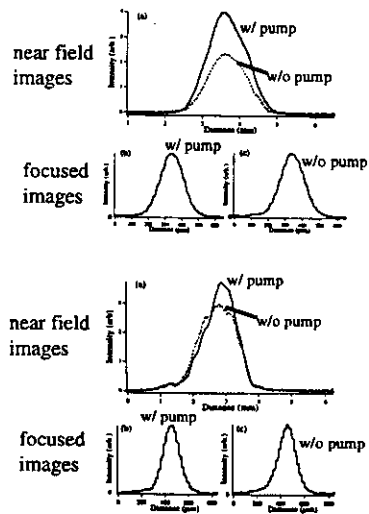
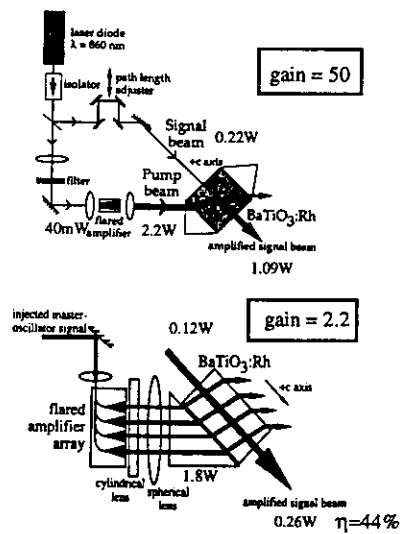
Use of photorefractive gain

- Coherent image amplification
- Beam cleanup
- Laser power combining
- Adaptive sensors/signal detection
- Pulse shaping
- Novelty filters
- Optical interconnect

Use of photorefractive loss

- Optical limiters
- Novelty filters
- Pulse shaping

Laser Beam Cleanup and Amplification



S.MacCormack *et al.*, Opt. Lett. 22, 227(1997)

Tracking Novelty Filters

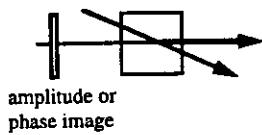
Function

- Detection of time-dependent features in a scene
- Temporal differentiation of a moving image

Implementation

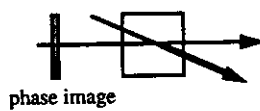
Use of Transient Photorefractive Gain

S.K.Kwong *et al.*,
JOSA B 5, 1788 (1988)



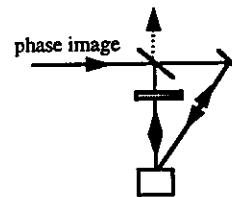
Use of Photorefractive Loss

M.Cronin-Golomb *et al.*,
Opt.Lett. 12, 1029 (1987)

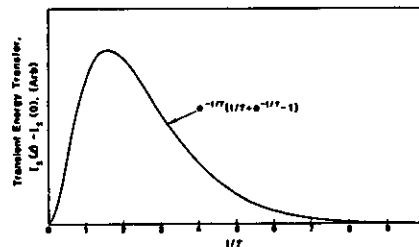
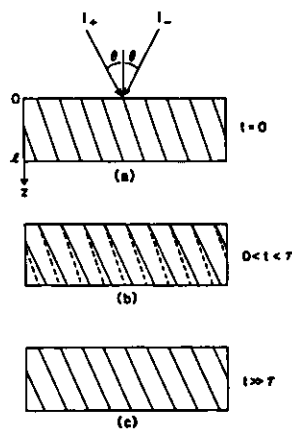


Use of Phase-Conjugate Waves

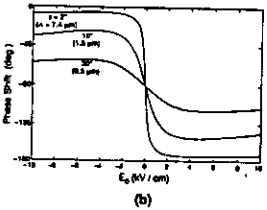
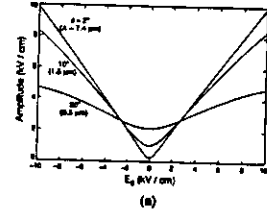
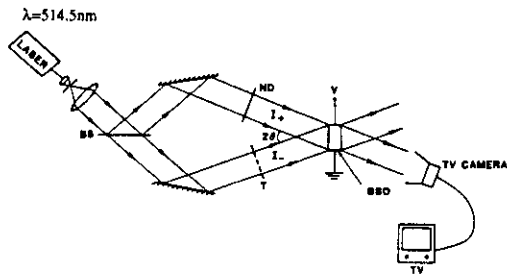
D.Z.Anderson *et al.*,
Opt.Lett. 12, 123 (1987)

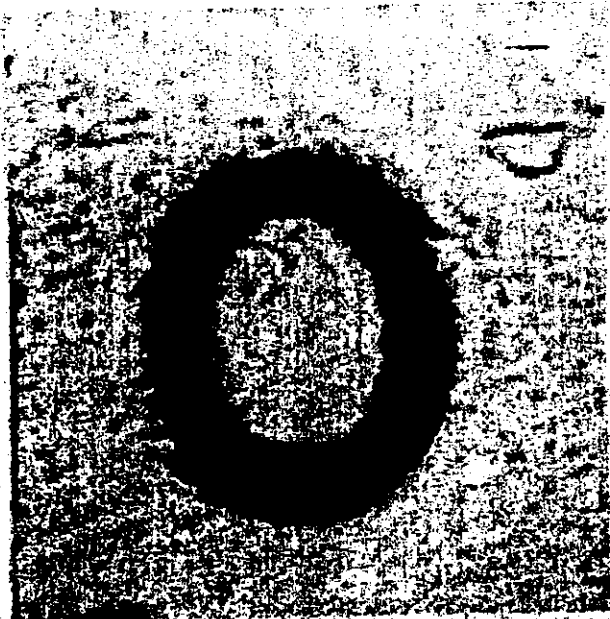


Tracking Novelty Filter Using Transient Energy Transfer – principle of operation –



Tracking Novelty Filter Using Transient Energy Transfer – experimental setup –

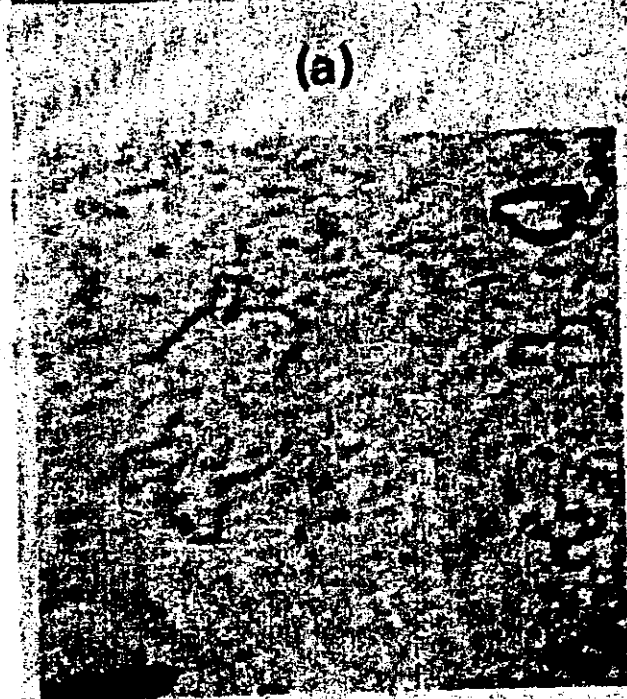




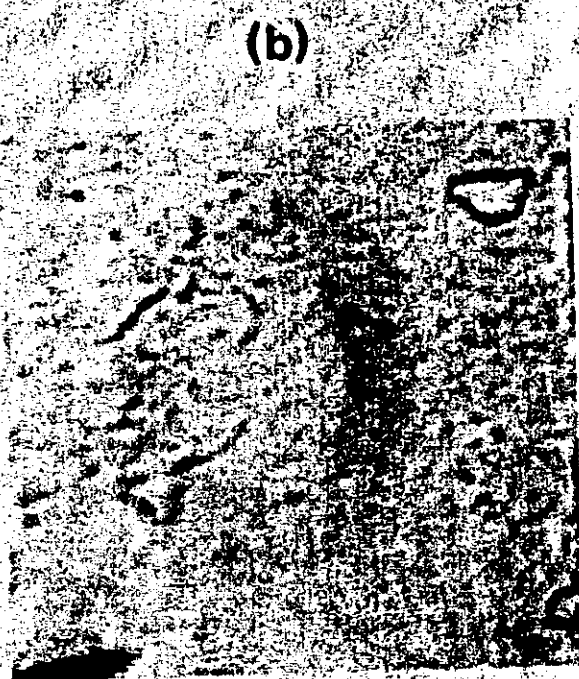
(a)



(b)



(c)

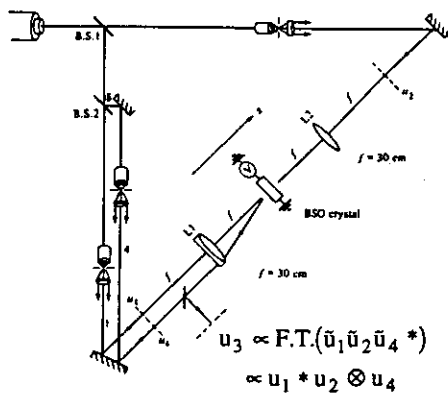


(d)

Applications of Photorefractive Volume Holograms

- Holographic data storage
- Image processing
- Matrix operation
- Spatial light modulation
- Optical pulse manipulations/diagnosis/storage
- Narrow band filters

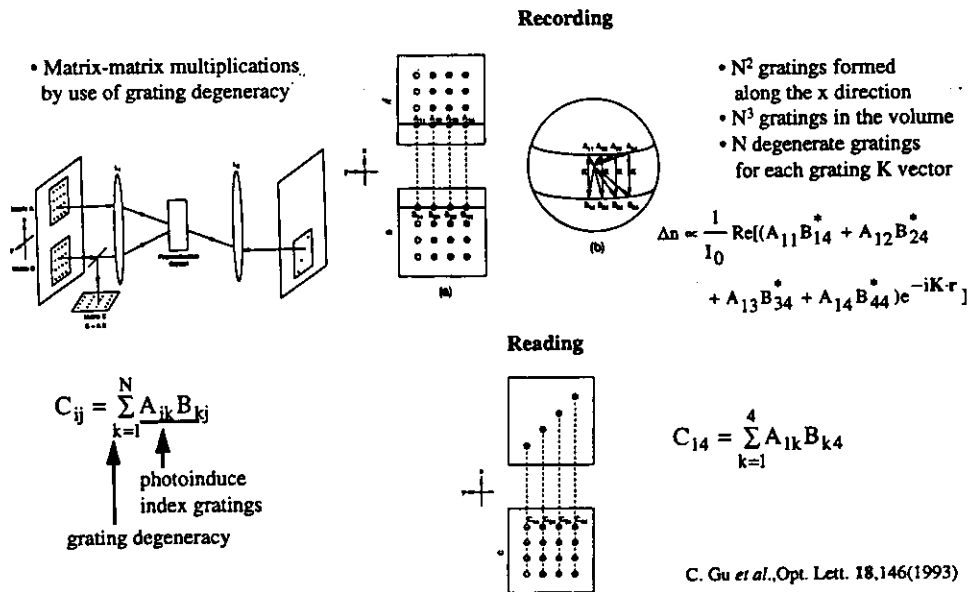
Real-Time Image Processing



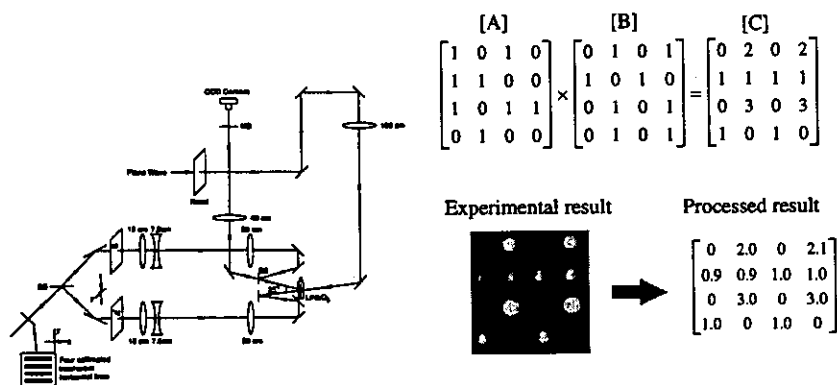
	U_1	U_2	U_4	U_3
1a)		DELTA FUNCTION		
1b)		DELTA FUNCTION	E	
1c)	C	DELTA FUNCTION	CAL TECH	
1d)	C		DELTA FUNCTION	

J.O.White *et al.*, APL40,450(1982)

Nonlinear Optical Matrix Processor – principle of operation –



Nonlinear Optical Matrix Processor – experimental result –



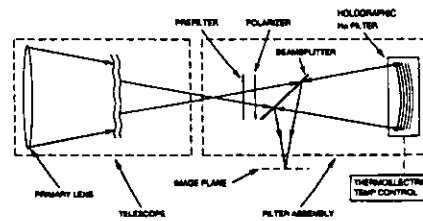
- Response time determined by the total intensity
- 10^{12} operations per second with 1msec response time at $1W/cm^2$ total intensity for 1000×1000 matrices .

C. Gu *et al.*, Opt. Lett. 18,146(1993)

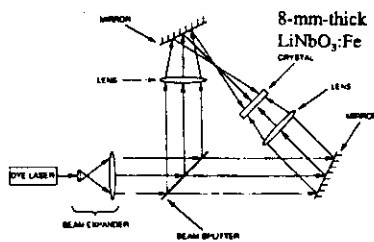
Volume Holographic Narrow-Band Optical Filter

Possible applications

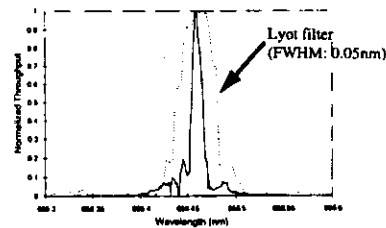
- solar astronomy
- spectroscopy
- sensors
- optical communications



Optical setup for writing the volume grating for the holographic H- α (656.28nm) filter



Peak reflectivity: > 50%
FWHM: 0.0125nm



G.A.Rakuljic and V.Leyva., Opt.Lett.18, 459(1993)

Applications of Phase Conjugation

Use of phase-conjugate waves

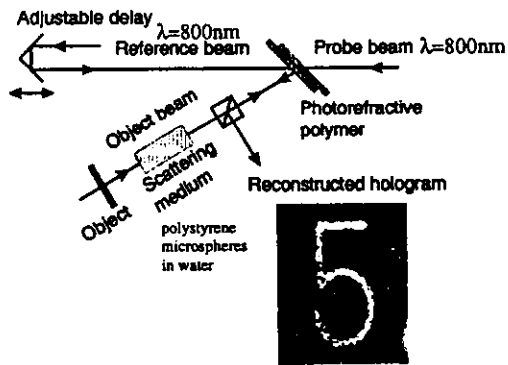
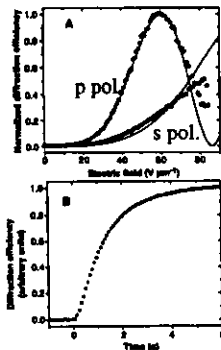
- Imaging through scattering media
- Lensless imaging/focusing
- Fiber-dispersion compensation
- Laser power combining/injection locking
- Associative memories
- Optical interconnect

Use as phase-conjugate interferometers

- Image subtraction, addition and inversion
- Novelty filters
- Adaptive sensors/signal detection
- Double-exposure/time-average holographic interferometry
- Measurement of thin-film properties

Holographic Time Gating for Imaging through Scattering Media

Photorefractive polymer
 DHHADC-MPN:PVK:TNFDM:ECz
 $\eta=74\%$ (59V/ μm) at $\lambda=830\text{nm}$



B. Kippelen *et al.*, Science 279, 54(1998)

Real-Time Image Addition, Subtraction and Inversion by Use of Phase Conjugate Mirror

Purpose

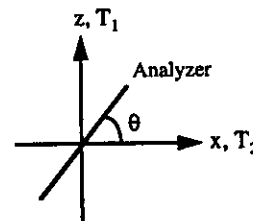
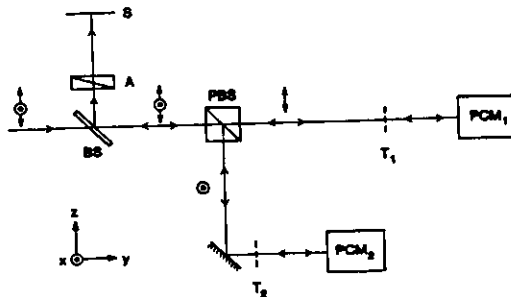
- compilation of composite images from separate inputs via *addition*
- difference detection, correction, and modification of images via *subtraction*
- deconvolution of images (e.g., deblurring of a distorted image) via *inversion*

$$I_{\text{out}} \propto |r_1|^2 \cos \theta |T_1|^2 + \rho \tan \theta |T_2|^2$$

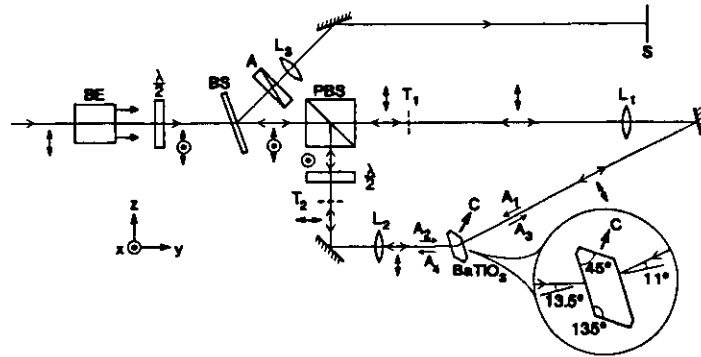
where

$$\rho = \text{const.} \times (r_1 / r_2)$$

- Subtraction : $\theta_{\text{sub}} = -\tan^{-1}(1/\rho)$
- Addition : $\theta_{\text{add}} = \tan^{-1}(1/\rho)$

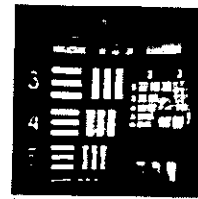
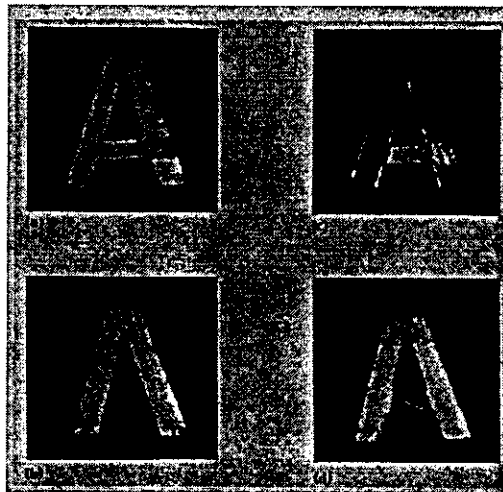


Experimental Setup

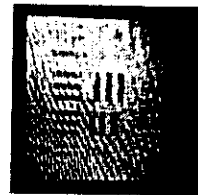


Y. Tomita et al., Appl. Phys. Lett. 52, 425 (1988)

Experimental Results



(a)



(b)

Y. Tomita et al., Appl. Phys. Lett. 52, 425 (1988)

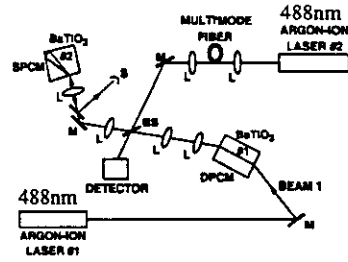
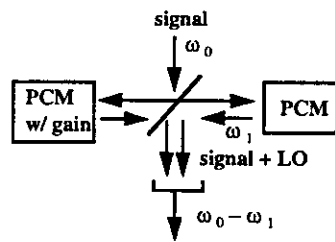
Adaptive Spatially Injection-Locked Heterodyne Receiver

Requirement for coherent optical receivers in intersatellit links and optical radars

- High degree of spatial mode matching between the signal and local oscillator fields

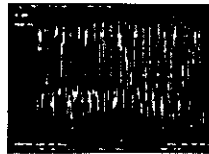


Use of nonlinear optical phase conjugation instead of using traditional methods such as deformable mirrors or coherent arrays

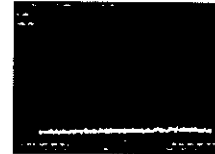


Heterodyne response

at $t = 10 \text{ min.}$



at $t = 0^+$



L.Adams and R.Bondurant, Opt. Lett. 18, 226 (1993)

